BQ25504 适用于能量收集应用且具有电池管理功能的超低功耗升压转换器

1 特性

- 借助高效直流/直流升压转换器/充电器可实现超低功耗
  - 从低压输入源进行持续能量收集：V_{IN} ≥ 130mV（典型值）
  - 超低静态电流：I_Q < 330nA（典型值）
  - 冷启动电压：V_{IN} ≥ 600mV（典型值）
- 可编程动态最大功率点跟踪 (MPPT)
  - 集成动态最大功率点跟踪功能，可实现对各种能量生成源的最优能量采集
  - 输入电压调节功能，可防止对输入源造成损坏
- 能量存储
  - 能量可存储到可重复充电的锂离子电池、薄膜电池、超级电容器或传统电容器中
- 电池充电和保护
  - 用户可编程的欠压和过压电平
  - 具有可编程过热关断功能的片上温度传感器
- 电池状态输出
  - 电池正常输出引脚
  - 可编程的阈值和迟滞
  - 功率损耗待定、随附报警功能的微控制器
  - 可用于启用或禁用系统负载

2 应用

- 能量收集
- 太阳能充电器
- 热电发电机 (TEG) 能量收集
- 无线传感器网络 (WSN)
- 工业监控
- 环境监控
- 桥梁和结构健康监测 (SHM)
- 智能楼宇控制
- 便携式和可佩戴式健康器件
- 娱乐系统遥控器

3 说明

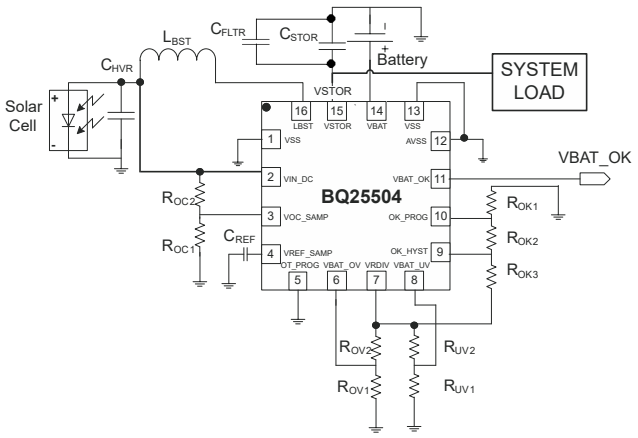
BQ25504 器件是智能化集成能源收集毫微功耗管理解决方案全新系列中的第一款产品，此类解决方案十分适合满足超低功耗应用的特殊需求。该器件经过专门设计，可高效收集和管理光伏（太阳能）发电机或热电发电机等各类直流源产生的微瓦 (μW) 至毫瓦 (mW) 级电能。BQ25504 在同类器件中，针对具有严苛功率和运行要求的产品和系统（如无线传感器网络 (WSN)），率先应用了高效的升压转换器/充电器。采用 BQ25504 设计的直流/直流升压转换器/充电器，仅需微瓦级功率即可开始工作。

升压转换器/充电器启动之后，能够高效地从热电发电机 (TEG) 或一块/两块太阳能面板等低压输出收集器中获得能量。升压转换器可通过低至 600mV 的 V_{IN} 启动，启动之后，可对低至 130mV 的 V_{IN} 继续进行能量收集。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
BQ25504	VQFN (16)	3.00mm x 3.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



太阳能应用电路

Table of Contents

4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision F (November 2019) to Revision G (August 2023) — **Page**

- Added "Connect to thermal pad." to AVSS and VSS pin descriptions in *Pin Functions* table 5
- Added lines from AVSS and VSS to GND in 图 11-1 30

Changes from Revision E (March 2019) to Revision F (November 2019) — **Page**

- 删除了“不推荐用于新设计” 1

Changes from Revision D (December 2018) to Revision E (March 2019) — **Page**

- 将*特性* 从“V_{IN} ≥ 80mV (典型值) ”更改为“V_{IN} ≥ 130mV (典型值) ” 1
- 将“V_{IN} 低至 330mV”更改为“V_{IN} 低至 600mV” (在*说明* 中) 1
- 将“可收集 V_{IN} 低至 80mV 的能量。”更改为“可收集 V_{IN} 低至 130mV 能量。” (在*说明* 中) 1
- Changed From: "330 mV typical,.." To: "600 mV typical,.." in the second paragraph of the *Overview* section 11
- Changed 图 8-1 14
- Changed From: "VIN(CS) = 330 mV typical." To: "VIN(CS) = 600 mV typical." in the second paragraph of the *Cold-Start Operation* section 15

Changes from Revision C (June 2015) to Revision D (December 2018) — **Page**

- 将*特性* 从“冷启动电压：V_{IN} ≥ 330mV (典型值) ”更改为“冷启动电压：V_{IN} ≥ 600mV (典型值) ” 1
- Changed the RGT Package appearance 5
- Moved T_{stg} to the *Absolute Maximum Ratings* table 6
- Changed Handling Ratings To: *ESD Ratings* 6
- Increased $V_{IN(CS)}$ From: TYP = 330 mV and MAX = 450 mV To: TYP = 600 mV and MAX = 700 mV in *节 7.5* table 7

Changes from Revision B (December 2014) to Revision C (June 2015) — **Page**

- Changed the Test Condition for $P_{IN(CS)}$ in the *节 7.5* 7

- Changed the values for $P_{IN(CS)}$ in the *节 7.5* From: TYP = 10, MAX = 50 To: TYP = 15, MAX deleted 7
- Changed C_{FLTR} To: C_{BYP} 图 9-1 21
- Changed CBYP = 0.1 µF To: CBYP = 0.01 µF in *节 9.2.1.2* 21
- Changed C_{FLTR} To: C_{BYP} in 图 9-8 24
- Changed CBYP = 0.1 µF To: CBYP = 0.01 µF in *节 9.2.2.2* 24
- Changed C_{FLTR} To: C_{BYP} in 图 9-15 26
- Changed CBYP = 0.1 µF To: CBYP = 0.01 µF in *节 9.2.3.2* 26
- Changed 图 11-1 30

Changes from Revision A (September 2012) to Revision B (December 2014) Page

- *添加了处理额定值 表、特性说明 部分、器件功能模式、应用和实现 部分、电源相关建议 部分、布局 部分、器件和文档支持 部分以及机械、封装和可订购信息 部分* 1

Changes from Revision * (October 2011) to Revision A (September 2012) Page

- Changed the *Cold -Start Operation* section 15
- Changed the Boost Converter, Charger Operation section 16
- Changed the Storage Element section 16
- Changed the CAPACITOR SELECTION section 20
- Added C_{FLTR} and Notes 1 and 2 to 图 9-1 21
- Added C_{FLTR} and Notes 1 and 2 to 图 9-8 24
- Added C_{FLTR} and Notes 1 and 2 to 图 9-15 26

5 说明（续）

BQ25504 还采用可编程的最大功率点跟踪采样网络，从而对器件的功率传输进行优化。VIN_DC 开路电压采样通过外部电阻进行编程，并由外部电容 (C_{REF}) 保持。

例如，对于最大功率点为 80% 开路电压的太阳能电池，可将电阻分压器设置为 VIN_DC 电压的 80%，此时该网络会将 VIN_DC 控制在采样的基准电压附近。或者，也可以通过微控制器 (MCU) 提供外部基准电压，以产生一个更为复杂的 MPPT 算法。

BQ25504 经设计可支持多种储能元件。能量收集器的能量源往往是不固定的，或者随时间变化的。系统通常需要特定类型的储能元件，例如可再充电电池、超级电容或传统电容。储能元件可确保在系统需要时提供恒定功率。凭借储能元件，系统还能够处理任何无法从输入源直接获取的峰值电流。

为了防止对客户的储能元件造成损坏，器件将参照用户编程的欠压 (UV) 和过压 (OV) 电平来监视最大电压和最小电压。

为了进一步帮助用户严格管理他们的能量预算，BQ25504 会在储能电池或电容器电压降至预设临界值以下时，切换电池正常状态标志，并向连接的微处理器发信号。该警告信号应触发负载电流下降，从而防止系统进入欠压状态。OV、UV 和电池正常阈值均单独进行编程。

BQ25504 的小型 16 引脚 3mm x 3mm VQFN 封装体中包含所有功能。

6 Pin Configuration and Functions

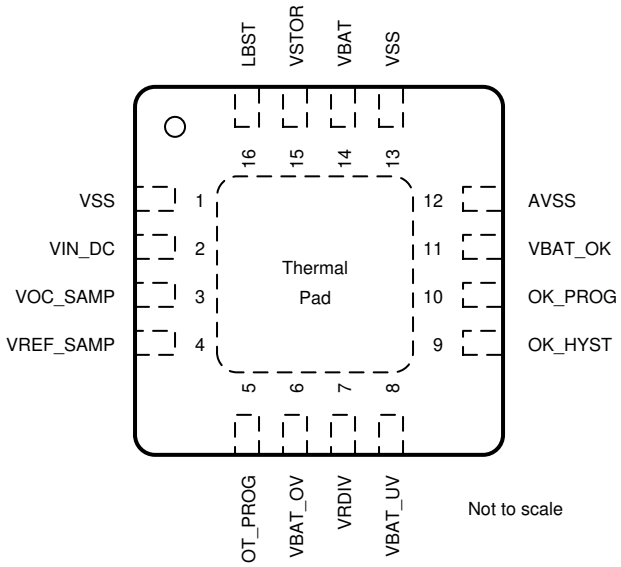


图 6-1. RGT Package 16 Pins Top View

表 6-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
AVSS	12	Supply	Signal ground connection for the device. Connect to thermal pad.
LBST	16	Input	Inductor connection for the boost charger switching node. Connect a 22 µH inductor between this pin and pin 2 (VIN_DC).
OK_HYST	9	Input	Connect to the mid-point of external resistor divider between VRDIV and GND for setting the VBAT_OK hysteresis threshold. If not used, connect this pin to GND.
OK_PROG	10	Input	Connect to the mid-point of external resistor divider between VRDIV and GND for setting the VBAT_OK threshold. If not used, connect this pin to GND.
OT_PROG	5	Input	Digital Programming input for IC overtemperature threshold. Connect to GND for 60 C threshold or VSTOR for 120 C threshold.
VBAT	14	I/O	Connect a rechargeable storage element with at least 100 uF of equivalent capacitance to this pin.
VBAT_OK	11	Output	Digital output for battery good indicator. Internally referenced to the VSTOR voltage. Leave floating if not used.
VBAT_OV	6	Input	Connect to the mid-point of external resistor divider between VRDIV and GND for setting the VSTOR = VBAT overvoltage threshold.
VBAT_UV	8	Input	Connect to the mid-point of external resistor divider between VRDIV and GND for setting the VBAT undervoltage threshold. The PFET between VBAT and VSTOR opens if the voltage on VSTOR is below this threshold.
VIN_DC	2	Input	DC voltage input from energy harvesters. Connect at least a 4.7 µF capacitor as close as possible between this pin and pin 1.
VOC_SAMP	3	Input	Sampling pin for MPPT network. Connect to the mid-point of external resistor divider between VIN_DC and GND for setting the MPP threshold voltage which will be stored on the VREF_SAMP pin. To disable the MPPT sampling circuit, connect to VSTOR.
VRDIV	7	Output	Resistor divider biasing voltage.
VREF_SAMP	4	Input	Connect a 0.01 µF low leakage capacitor from this pin to GND to store the voltage to which VIN_DC will be regulated. This voltage is provided by the MPPT sample circuit. When MPPT is disabled, either use an external voltage source to provide this voltage or tie this pin to GND to disable input voltage regulation (i.e. operate from a low impedance power supply).
VSS	1	Input	General ground connection for the device. Connect to thermal pad.
VSS	13	Supply	General ground connection for the device. Connect to thermal pad.
VSTOR	15	Output	Connection for the output of the boost charger, which is typically connected to the system load. Connect at least a 4.7 µF capacitor in parallel with a 0.1 µF capacitor as close as possible to between this pin and pin 1 (VSS).

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Input voltage	VIN_DC, VOC_SAMP, VREF_SAMP, VBAT_OV, VBAT_UV, VRDIV, OK_HYST, OK_PROG, VBAT_OK, VBAT, VSTOR, LBST(2)	–0.3	5.5	V
Peak Input Power, P_{IN_PK}			400	mW
Operating junction temperature range, T_J		–40	125	°C
Storage temperature range, T_{stg}		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute – maximum – rated conditions for extended periods may affect device reliability.
(2) All voltage values are with respect to V_{SS}/ground terminal.

7.2 ESD Ratings

			MIN	MAX	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)		2	kV
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)		500	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT
$V_{IN\ (DC)}$	DC input voltage into VIN_DC(1)	0.13		3	V
VBAT	Battery voltage range(2)	2.5		5.25	V
C_{HVR}	Input capacitance	4.23	4.7	5.17	µF
C_{STOR}	Storage capacitance	4.23	4.7	5.17	µF
C_{BAT}	Battery pin capacitance or equivalent battery capacity	100			µF
C_{REF}	Sampled reference storage capacitance	9	10	11	nF
$R_{OC1} + R_{OC2}$	Total resistance for setting for MPPT reference.	18	20	22	MΩ
$R_{OK}1 + R_{OK}2 + R_{OK3}$	Total resistance for setting reference voltage.	9	10	11	MΩ
$R_{UV1} + R_{UV2}$	Total resistance for setting reference voltage.	9	10	11	MΩ
$R_{OV1} + R_{OV2}$	Total resistance for setting reference voltage.	9	10	11	MΩ
L_{BST}	Input inductance	19.8	22	24.2	µH
T_A	Operating free air ambient temperature	–40		85	°C
T_J	Operating junction temperature	–40		105	°C

(1) Maximum input power ⩽ 300 mW. Cold start has been completed
(2) VBAT_OV setting must be higher than VIN_DC

7.4 Thermal Information

THERMAL METRIC(1)		BQ25504 RGT (QFN) 16 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	48.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	63.9	
$R_{\theta JB}$	Junction-to-board thermal resistance	22	
ψ_{JT}	Junction-to-top characterization parameter	1.8	
ψ_{JB}	Junction-to-board characterization parameter	22	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	6.5	

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, .

7.5 Electrical Characteristics

Over recommended temperature range, typical values are at T_A = 25°C. Unless otherwise noted, specifications apply for conditions of VIN_DC = 1.2V, VBAT = VSTOR = 3V. External components L_{BST} = 22 µH, C_{HVR} = 4.7 µF C_{STOR}= 4.7 µF.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
BOOST CONVERTER \ CHARGER STAGE						
$V_{IN(DC)}$	DC input voltage into VIN_DC	Cold-start completed	130		3000	mV
$I_{IN(DC)}$	Peak Current flowing from V_{IN} into VIN_DC input	0.5V < V_{IN} < 3 V; VSTOR = 4.2 V		200	300	mA
P_{IN}	Input power range for normal charging	VBAT > VIN_DC; VIN_DC = 0.5 V	0.01		300	mW
$V_{IN(CS)}$	Cold-start Voltage. Input voltage that will start charging of VSTOR	VBAT < VBAT_UV; VSTOR = 0 V; 0°C < T_A < 85°C		600	700	mV
$P_{IN(CS)}$	Minimum cold-start input power to start normal charging	VBAT < $VSTOR_{(CHGEN)}$ VIN_DC clamped to VIN_CS by cold start circuit VBAT = 100 µF ceramic		15		µW
V_{STOR_CHGEN}	Voltage on VSTOR when cold start operation ends and normal charger operation begins		1.6	1.77	1.95	V
$R_{BAT(on)}$	Resistance of switch between VBAT and VSTOR when turned on.	VBAT = 4.2 V; VSTOR load = 50 mA			2	Ω
$R_{DS(on)}$	Charger Low Side switch ON resistance	VBAT = 2.1 V			2	Ω
		VBAT = 4.2 V			2	
	Charger rectifier High Side switch ON resistance	VBAT = 2.1 V			5	Ω
		VBAT = 4.2 V			5	
f_{SW_BST}	Boost converter mode switching frequency				1	MHz
BATTERY MANAGEMENT						
I_{VBAT}	Leakage on VBAT pin	VBAT = 2.1 V; VBAT_UV = 2.3 V, T_J = 25°C VSTOR = 0 V		1	5	nA
		VBAT = 2.1 V; VBAT_UV = 2.3 V, –40°C < T_J < 65°C, VSTOR = 0 V			80	nA
I_{VSTOR}	VSTOR Quiescent current Charger Shutdown in UV Condition	VIN_DC = 0V; VBAT < VBAT_UV = 2.4V; VSTOR = 2.2V, No load on VBAT		330	750	nA
	VSTOR Quiescent current Charger Shutdown in OV Condition	VIN_DC = 0V, VBAT > VBAT_OV, VSTOR = 4.25, No load on VBAT		570	1400	nA
V_{BAT_OV}	Programmable voltage range for overvoltage threshold (Battery voltage is rising)	VSTOR increasing	2.5		5.25	V
$V_{BAT\_OV\_HYST}$	Battery voltage overvoltage hysteresis threshold (Battery voltage is falling), internal threshold	VSTOR decreasing	18	35	89	mV
V_{BAT_UV}	Programmable voltage range for under voltage threshold (Battery voltage is falling)	VSTOR decreasing; VBAT_UV > V_{Bias}	2.2		VBAT_OV	V
$V_{BAT\_UV\_HYST}$	Battery under voltage threshold hysteresis, internal thershold	VSTOR increasing	40	80	125	mV
V_{BAT_OK}	Programmable voltage range for threshold voltage for high to low transition of digital signal indicating battery is OK,	VSTOR decreasing	VBAT_UV		VBAT_OV	V
$V_{BAT\_OK\_HYST}$	Programmable voltage range for threshold voltage for low to high transition of digital signal indicating battery is OK,	VSTOR increasing	50		VBAT_OV-VBAT_UV	mV
$V_{BAT\_ACCURACY}$	Overall Accuracy for threshold values, UV, OV, VBAT_OK	Selected resistors are 0.1% tolerance	–5%		5%	

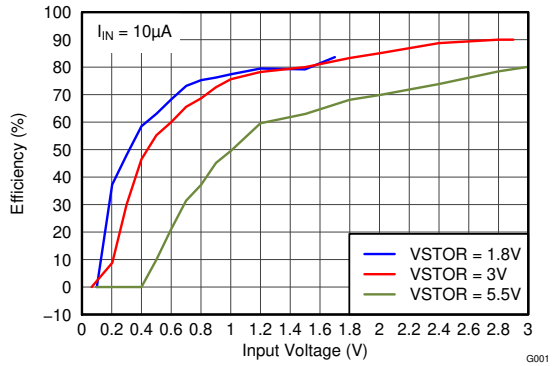
7.5 Electrical Characteristics (continued)

Over recommended temperature range, typical values are at T_A = 25°C. Unless otherwise noted, specifications apply for conditions of VIN_DC = 1.2V, VBAT = VSTOR = 3V. External components L_{BST} = 22 µH, C_{HVR} = 4.7 µF C_{STOR}= 4.7 µF.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{BAT_OKH}	VBAT OK (High) threshold voltage	Load = 10 µA			VSTOR-200mV	V
V_{BAT_OKL}	VBAT OK (Low) threshold voltage	Load = 10 µA			100	mV
TSD_PROTL	The temperature at which the boost converter is disabled and the switch between VBAT and VSTOR is disconnected to protect the battery	OT_Prog = LO		65		°C
TSD_PROTH		OT_Prog = HI		120		
OT_Prog	Voltage for OT_PROG High setting		2			V
	Voltage for OT_PROG Low setting				0.3	V
BIAS and MPPT CONTROL STAGE						
VOC_sample	Sampling period of VIN_DC open circuit voltage			16		s
VOC_Settling	Sampling period of VIN_DC open circuit voltage			256		ms
VIN_Reg	Regulation of VIN_DC during charging	0.5 V <V_{IN} < 3 V; I_{IN} (DC) = 10 mA	–10%		10%	
VIN_shutoff	DC input voltage into VIN_DC when charger is turned off		40	80	130	mV
MPPT_Disable	Threshold on VOC_SAMP to disable MPPT functionality		VSTOR-15 mV			V
VBIAS	Voltage node which is used as reference for the programmable voltage thresholds	VIN_DC ⩾ 0.5V; VSTOR ⩾ 1.8 V	1.21	1.25	1.27	V

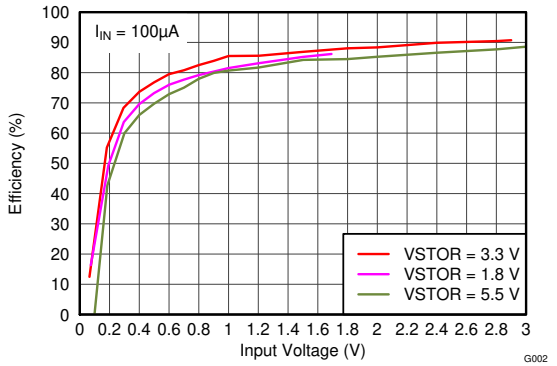
7.6 Typical Characteristics

VSTOR = Keithley Sourcemeter configured to measure current and voltage source set to hold the VSTOR voltage = 1.8 V, 3.0 V or 5.5 V; VBAT_OV = 5.5 V and measurement taken between MPPT measurements.



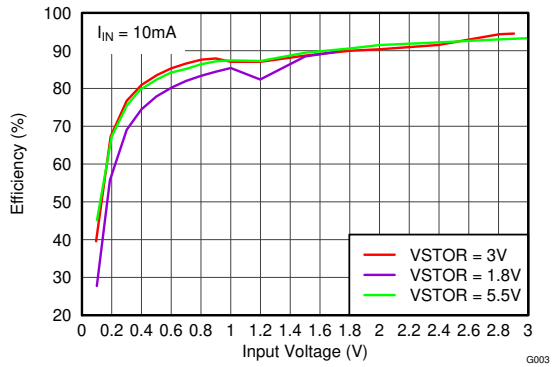
VIN_DC = Keithley Source Meter configured with I_{COMP} = 10 µA and outputing 0 to 3.0 V

图 7-1. Efficiency vs Input Voltage



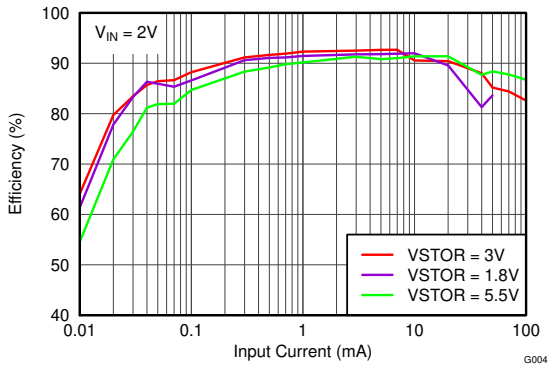
VIN_DC = Keithley Source Meter configured with I_{COMP} = 100 µA and voltage source varied from 0.1 V to 3.0 V

图 7-2. Efficiency vs Input Voltage



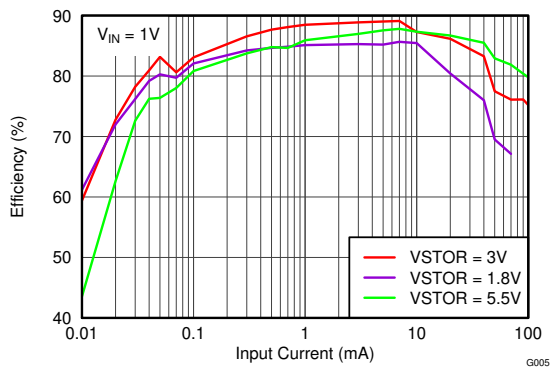
VIN_DC = Keithley Source Meter configured with I_{COMP} = 10 mA and voltage source varied from 0.1 V to 3.0 V

图 7-3. Efficiency vs Input Voltage



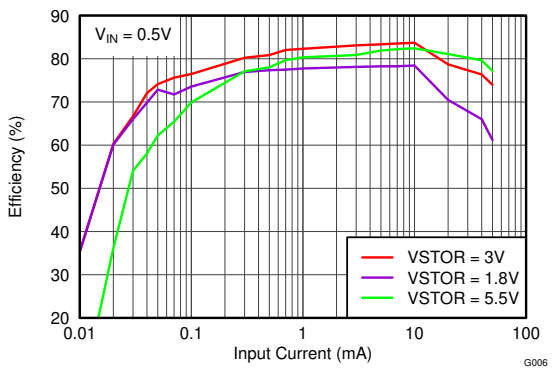
VIN_DC = Keithley Source Meter configured with voltage source = 2.0 V and I_{COMP} varied from 0.01 mA to 100 mA

图 7-4. Efficiency vs Input Current



VIN_DC = Keithley Source Meter configured with voltage source = 1.0 V and I_{COMP} varied from 0.01 mA to 100 mA

图 7-5. Efficiency vs Input Current

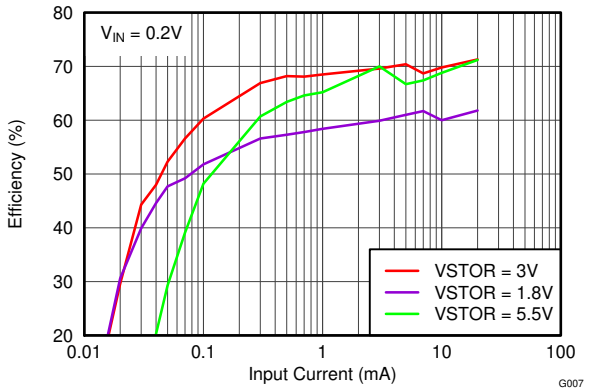


VIN_DC = Keithley Source Meter configured with voltage source = 0.5 V and I_{COMP} varied from 0.01 mA to 100 mA

图 7-6. Efficiency vs Input Current

7.6 Typical Characteristics (continued)

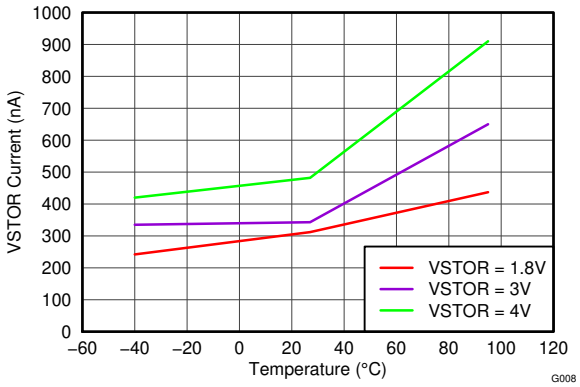
VSTOR = Keithley Sourcemeter configured to measure current and voltage source set to hold the VSTOR voltage = 1.8 V, 3.0 V or 5.5 V; VBAT_OV = 5.5 V and measurement taken between MPPT measurements.



VIN_DC = Keithley Source Meter configured with voltage source = 0.2 V and I_{COMP} varied from 0.01 mA to 100 mA

VSTOR = Keithley Source Meter configured to measure current and voltage source set to hold the VSTOR voltage = 2.0 V, 3.0 V or 5.5 V

图 7-7. Efficiency vs Input Current



VIN_DC = floating

VBAT = Keithley Sourcemeter configured to measure current and voltage source varied from 1.8 V, 3 V, or 4 V

图 7-8. VSTOR Quiescent Current vs Temperature

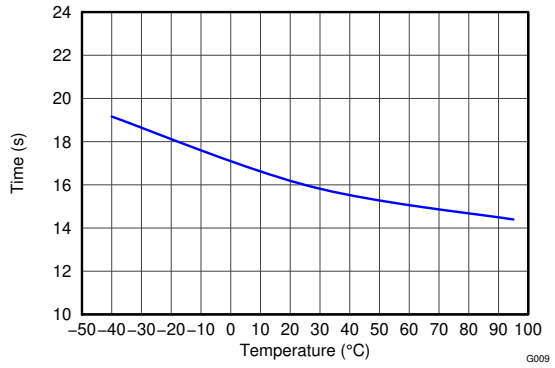


图 7-9. Sample Period vs Temperature

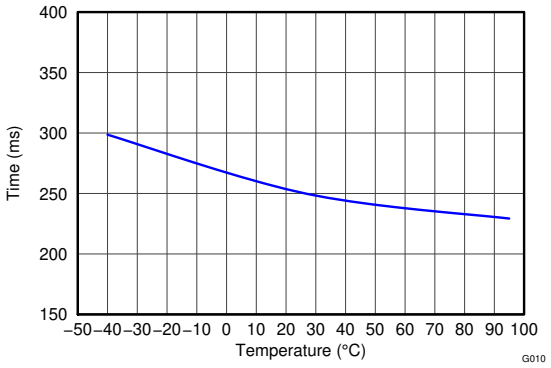


图 7-10. Settling Period vs Temperature

8 Detailed Description

8.1 Overview

The BQ25504 is the first of a new family of intelligent integrated energy harvesting Nano-Power management solutions that are well suited for meeting the special needs of ultra low power applications. The product is specifically designed to efficiently acquire and manage the microwatts (μW) to miliwatts (mW) of power generated from a variety of DC sources like photovoltaic (solar) or thermal electric generators (TEGs). The BQ25504 is a highly efficient boost charger targeted toward products and systems, such as wireless sensor networks (WSN) which have stringent power and operational demands. The design of the BQ25504 starts with a DCDC boost charger that requires only microwatts of power to begin operating.

Once the VSTOR voltage is above VSTOR_CHGEN (1.8 V typical), for example, after a partially discharged battery is attached to VBAT, the boost charger can effectively extract power from low voltage output harvesters such as TEGs or single or dual cell solar panels outputting voltages down to VIN(DC) (130 mV minimum). When starting from VSTOR = VBAT < 100 mV, the cold start circuit needs at least VIN(CS), 600 mV typical, to charge VSTOR up to 1.8 V.

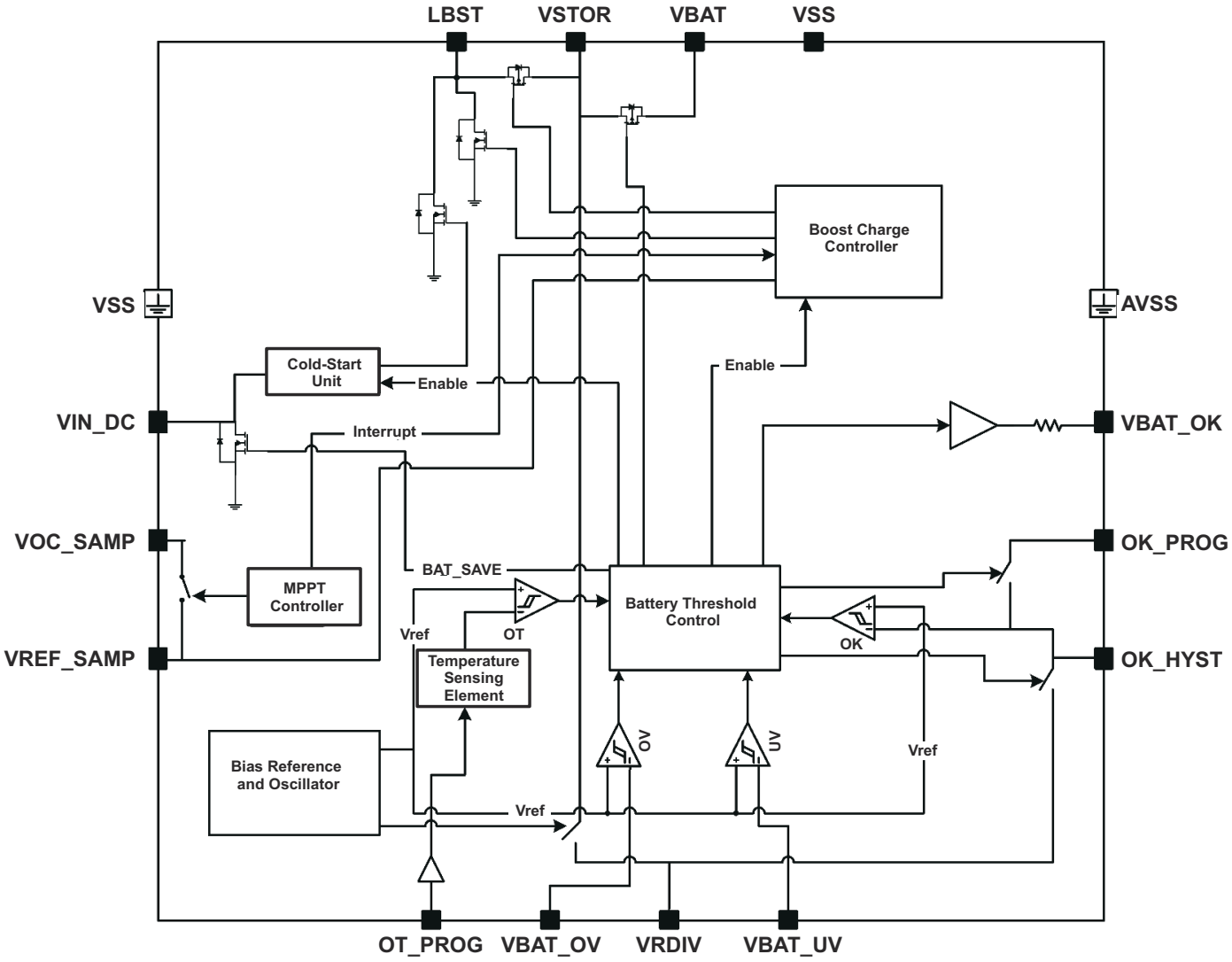
The BQ25504 implements a programmable maximum power point tracking (MPPT) sampling network to optimize the transfer of power into the device. Sampling of the VIN_DC open circuit voltage is programmed using external resistors, and that sample voltage is held with an external capacitor connected to the VREF_SAMP pin.

For example solar cells that operate at maximum power point (MPP) of 80% of their open circuit voltage, the resistor divider can be set to 80% of the VIN_DC voltage and the network will control the VIN_DC to operate near that sampled reference voltage. Alternatively, an external reference voltage can be applied directly to the VREF_SAMP pin by a MCU to implement a more complex MPPT algorithm.

The BQ25504 was designed with the flexibility to support a variety of energy storage elements. The availability of the sources from which harvesters extract their energy can often be sporadic or time-varying. Systems will typically need some type of energy storage element, such as a re-chargeable battery, super capacitor, or conventional capacitor. The storage element will make certain constant power is available when needed for the systems. The storage element also allows the system to handle any peak currents that can not directly come from the input source. To prevent damage to the storage element, both maximum and minimum voltages are monitored against the user programmable undervoltage (VBAT_UV) and overvoltage (VBAT_OV) levels.

To further assist users in the strict management of their energy budgets, the BQ25504 toggles the battery good flag to signal an attached microprocessor when the voltage on an energy storage battery or capacitor has dropped below a pre-set critical level. This should trigger the shedding of load currents to prevent the system from entering an undervoltage condition. The OV and battery good (VBAT_OK) thresholds are programmed independently.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Maximum Power Point Tracking

Maximum power point tracking (MPPT) is implemented in order to maximize the power extracted from an energy harvester source. The boost converter indirectly modulates the input impedance of the main boost charger by regulating the charger's input voltage, as sensed by the VIN_DC pin, to the sampled reference voltage stored on the VREF_SAMP pin. The MPPT circuit obtains a new reference voltage every 16 s (typical) by periodically disabling the charger for 256 ms (typical) and sampling a fraction of the harvester's open-circuit voltage (VOC). For solar harvesters, the maximum power point is typically 70%-80% of VOC and for thermoelectric harvesters, the MPPT is typically 50%. The exact ratio for MPPT can be optimized to meet the needs of the input source being used by connecting external resistors R_{OC1} and R_{OC2} between VIN_DC and GND with mid-point at VOC_SAMP.

$$VREF\_SAMP = VIN\_DC(OpenCircuit)\left(\frac{R_{OC1}}{R_{OC1} + R_{OC2}}\right) \quad (1)$$

Spreadsheet SLUC484 provides help on sizing and selecting the resistors.

The internal MPPT circuitry and the periodic sampling of VIN_DC can be disabled by tying the VOC_SAMP pin to VSTOR. An external reference voltage can be fed to the VREF_SAMP pin. The boost converter will then regulate VIN_DC to the externally provided reference. If input regulation is not desired (i.e. the input source is a low-impedance output battery or power supply instead of a high impedance output energy harvester), VREF_SAMP can be tied to GND.

8.3.2 Battery Undervoltage Protection

To prevent rechargeable batteries from being deeply discharged and damaged, and to prevent completely depleting charge from a capacitive storage element, the undervoltage (VBAT_UV) threshold must be set using external resistors. The VBAT_UV threshold voltage when the battery voltage is decreasing is given by 方程式 2:

$$VBAT\_UV = VBIAS\left(1 + \frac{R_{UV2}}{R_{UV1}}\right) \quad (2)$$

The sum of the resistors is recommended to be no higher than 10 MΩ that is, $R_{UV1} + R_{UV2} = 10\ M\Omega$. Spreadsheet SLURAQ1 provides help on sizing and selecting the resistors.

The undervoltage threshold when the battery voltage is increasing is VBAT_UV plus an internal hysteresis voltage denoted by VBAT_UV_HYST. For the VBAT_UV feature to function properly, the load must be connected to the VSTOR pin while the storage element should be connected to the VBAT pin. Once the VSTOR pin voltage goes above VBAT_UV plus VBAT_UV_HYST threshold, the VSTOR pin and the VBAT pins are effectively shorted through an internal PMOS FET. The switch remains closed until the VSTOR pin voltage falls below the VBAT_UV threshold. The VBAT_UV threshold should be considered a fail safe to the system. The system load should be removed or reduced based on the VBAT_OK threshold which should be set above the VBAT_UV threshold.

8.3.3 Battery Overvoltage Protection

To prevent rechargeable batteries from being exposed to excessive charging voltages and to prevent over charging a capacitive storage element, the over-voltage (VBAT_OV) threshold level must be set using external resistors. This is also the voltage value to which the charger will regulate the VSTOR/VBAT pin when the input has sufficient power. The VBAT_OV threshold when the battery voltage is rising is given by 方程式 3:

$$VBAT\_OV = \frac{3}{2}VBIAS\left(1 + \frac{R_{OV2}}{R_{OV1}}\right) \quad (3)$$

The sum of the resistors is recommended to be no higher 10 MΩ that is, $R_{OV1} + R_{OV2} = 10\ M\Omega$. Spreadsheet SLURAQ1 provides help with sizing and selecting the resistors.

The overvoltage threshold when the battery voltage is decreasing is given by VBAT_OV - VBAT_OV_HYST. Once the voltage at the battery reaches the VBAT_OV threshold, the boost converter is disabled. The charger will start again once the battery voltage drop by VBAT_OV_HYST. When there is excessive input energy, the VBAT pin voltage will ripple between the VBAT_OV and the VBAT_OV - VBAT_OV_HYST levels.

CAUTION

If VIN_DC is higher than VSTOR and VSTOR is higher than VBAT_OV, the input VIN_DC is pulled to ground through a small resistance to stop further charging of the attached battery or capacitor. It is critical that if this case is expected, the impedance of the source attached to VIN_DC be higher than 20 Ω and not a low impedance source.

8.3.4 Battery Voltage in Operating Range (VBAT_OK Output)

The IC allows the user to set a programmable voltage independent of the overvoltage and undervoltage settings to indicate whether the VSTOR voltage (and therefore the VBAT voltage when the PFET between the two pins is turned on) is at an acceptable level. When the battery voltage is decreasing the threshold is set by 方程式 4:

$$VBAT\_OK\_PROG = VBIAS\left(1 + \frac{R_{OK2}}{R_{OK1}}\right) \quad (4)$$

When the battery voltage is increasing, the threshold is set by 方程式 5:

$$VBAT\_OK\_HYST = VBIAS\left(1 + \frac{R_{OK2} + R_{OK3}}{R_{OK1}}\right) \quad (5)$$

The sum of the resistors are recommended to be approximately 10 MΩ i.e., R_{OK1} + R_{OK2} + R_{OK3}= 10 MΩ. Spreadsheet SLURAQ1 provides help on sizing and selecting the resistors.

The logic high level of this signal is equal to the VSTOR voltage and the logic low level is ground. The logic high level has ~20 KΩ internally in series to limit the available current to prevent MCU damage until it is fully powered. The VBAT_OK_PROG threshold must be greater than or equal to the UV threshold. 图 8-1 shows the relative position of the various threshold voltages.

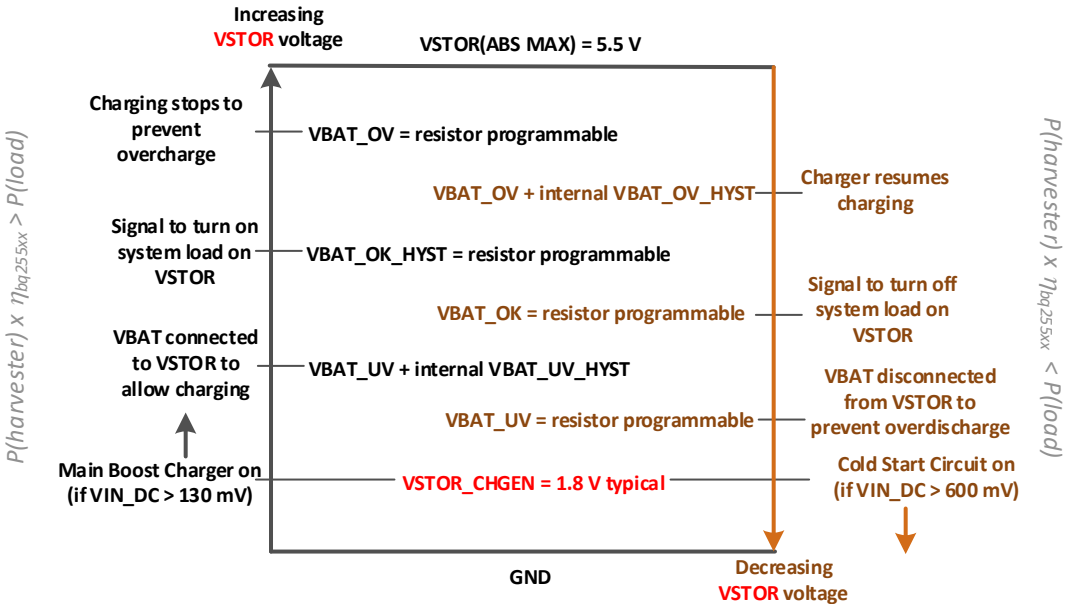


图 8-1. Summary of VSTOR Threshold Voltages

8.3.5 Nano-Power Management and Efficiency

The high efficiency of the BQ25504 charger is achieved via the proprietary Nano-Power management circuitry and algorithm. This feature essentially samples and holds the VSTOR voltage in order to reduce the average quiescent current. That is, the internal circuitry is only active for a short period of time and then off for the remaining period of time at the lowest feasible duty cycle. A portion of this feature can be observed in 图 9-6 where the VRDIV node is monitored. Here the VRDIV node provides a connection to the VSTOR voltage (first pulse) and then generates the reference levels for the VBAT_OV and VBAT_OK resistor dividers for a short period of time. The divided down values at each pin arecompared against VBIAS as part of the hysteretic control. Since this biases a resistor string, the current through these resistors is only active when the Nano-

Power management circuitry makes the connection—hence reducing the overall quiescent current due to the resistors. This process repeats every 64 ms.

The BQ25504 boost charger efficiency is shown for various input power levels in 图 7-1 through 图 7-7. All data points were captured by averaging the overall input current. This must be done due to the periodic biasing scheme implemented via the Nano-Power management circuitry. In order to properly measure the resulting input current when calculating the output to input efficiency, the input current efficiency data was gathered using a source meter set to average over at least 50 samples. Quiescent current curves into VSTOR over temperature and voltage is shown at 图 7-8.

8.4 Device Functional Modes

The BQ25504 has three functional modes: cold-start operation, main boost charger enabled and thermal shutdown. The cold start circuitry is powered from VIN_DC. The main boost charger circuitry is powered from VSTOR while the boost power stage is powered from VIN_DC. Details of entering and exiting each mode are explained below.

8.4.1 Cold-Start Operation (VSTOR < VSTOR_CHGEN, VIN_DC > VIN(CS) and PIN > PIN(CS))

Whenever VSTOR < VSTOR_CHGEN, VIN_DC ≥ VIN(CS) and PIN > PIN(CS), the cold-start circuit is on. This could happen when there is not input power at VIN_DC to prevent the load from discharging the battery or during a large load transient on VSTOR. During cold start, the voltage at VIN_DC is clamped to VIN(CS) so the energy harvester's output current is critical to providing sufficient cold start input power, PIN(CS) = VIN(CS) X IIN(CS). The cold-start circuit is essentially an unregulated, hysteretic boost converter with lower efficiency compared to the main boost charger. None of the other features function during cold start operation. The cold start circuit's goal is to charge VSTOR higher than VSTOR_CHGEN so that the main boost charger can operate. When a depleted storage element is initially attached to VBAT, as shown in 图 8-2 and the harvester can provide a voltage > VIN(CS) and total power at least > PIN(CS), assuming minimal system load or leakage at VSTOR and VBAT, the cold start circuit can charge VSTOR above VSTOR_CHGEN. Once the VSTOR voltage reaches the VSTOR_CHGEN threshold, the IC

1. first performs an initialization pulse on VRDIV to reset the feedback voltages,
2. then disables the charger for 32 ms (typical) to allow the VIN_DC voltage to rise to the harvester's open-circuit voltage which will be used as the input voltage regulation reference voltage until the next MPPT sampling cycle and
3. lastly performs its first feedback sampling using VRDIV, approximately 64 ms after the initialization pulse.

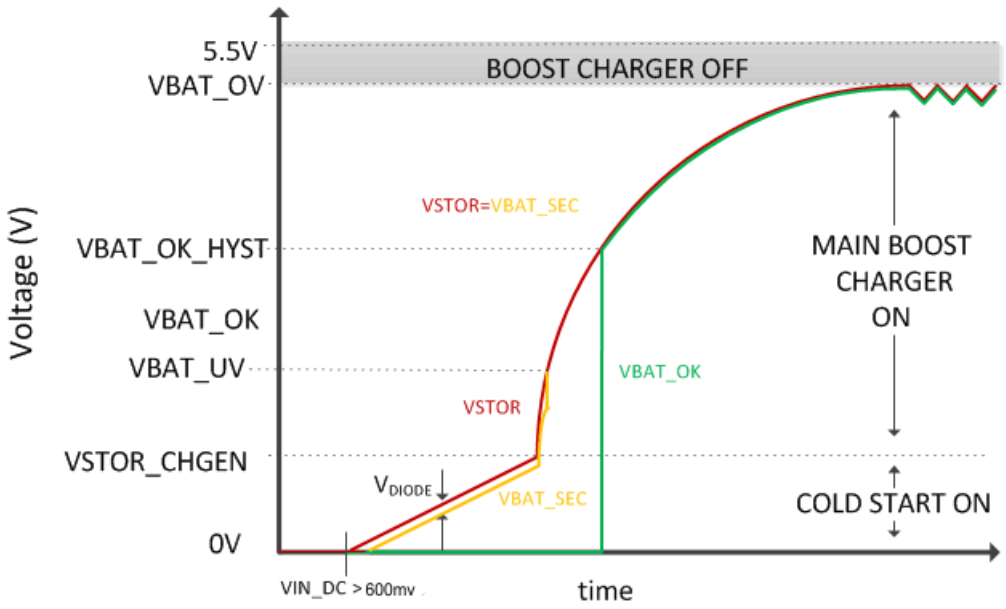


图 8-2. Charger Operation After a Depleted Storage Element is Attached and Harvester is Available

The energy harvester must supply sufficient power for the IC to exit cold start. Due to the body diode of the PFET connecting VSTOR and VBAT, the cold start circuit must charge both the capacitor on CSTOR up to the VSTOR_CHGEN and the storage element connected to VBAT up to VSTOR_CHGEN less a diode drop. When a rechargeable battery with an open protector is attached, the intial charge time is typically short due to the minimum charge needed to close the battery's protector FETs. When large, discharged super capacitors with high DC leakage currents are attached, the intial charge time can be signficant.

When the VSTOR voltage reaches VSTOR_CHGEN, the main boost charger starts up. When the VSTOR voltage rises to the VBAT_UV threshold, the PMOS switch between VSTOR and VBAT turns on, which provides additional loading on VSTOR and could result in the VSTOR voltage dropping below both the VBAT_UV threshold and the VSTOR_CHGEN voltage, especially if system loads on VSTOR or VBAT are active during this time. Therefore, it is not uncommon for the VSTOR voltage waveform to have incremental pulses (i.e. stair steps) as the IC cycles between cold-start and main boost charger operation before eventually maintaing VSTOR above VSTOR_CHGEN.

The cold start circuit initially clamps VIN_DC to VIN(CS) = 600 mV typical. If sufficient input power (i.e.,output current from the harvester clamped to VIN(CS)) is not available, it is possible that the cold start circuit cannot raise the VSTOR voltage above VSTOR_CHGEN in order for the main boost conveter to start up. It is highly recommended to add an external PFET between the system load and VSTOR. An inverted VBAT_OK signal can be used to drive the gate of this system-isolating, external PFET. See the *节 10* section for guidance on minimum input power requirements.

8.4.2 Main Boost Charger Enabled (VSTOR > VSTOR_CHGEN, VIN_DC > VIN(DC) and $\overline{EN}$ = LOW)

One way to avoid cold start is to attach a partially charged storage element as shown in 图 8-3.

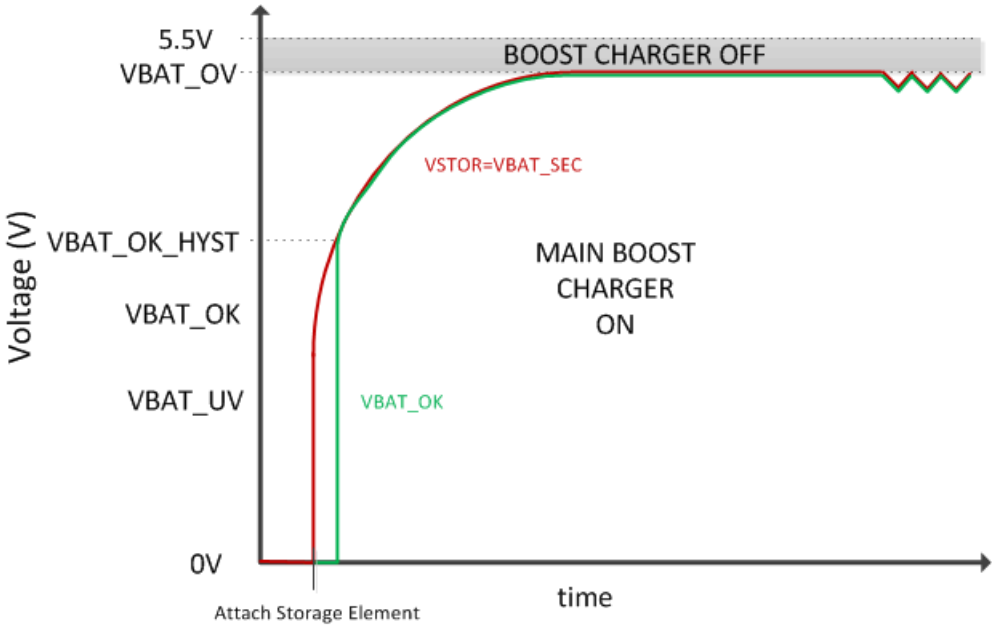


图 8-3. Charger Operation after a Partially Charged Storage Element is Attached and Harvester Power is Available

When no input source is attached, the VSTOR node should be discharged to ground before attaching a storage element. Hot-plugging a storage element that is charged (e.g., the battery protector PFET is closed) and with the VSTOR node more than 100 mV above ground results in the PFET between VSTOR and VBAT remaining off until an input source is attached.

Assuming the voltages on VSTOR and VBAT are both below 100mV, when a charged storage element is attached (i.e. hot-plugged) to VBAT, the IC.

1. first turns on the internal PFET between the VSTOR and VBAT pins for $t_{BAT\_HOT\_PLUG}$ (45ms) in order to charge VSTOR to VSTOR_CHGEN then turns off the PFET to prevent the battery from overdischarge,
2. then performs an initialization pulse on VRDIV to reset the feedback voltages,
3. then disables the charger for 32 ms (typical) to allow the VIN_DC voltage to rise to the harvester's open-circuit voltage which will be used as the input voltage regulation reference voltage until the next MPPT sampling cycle and
4. lastly performs its first feedback sampling using VRDIV, approximately 64 ms after the initialization pulse.

If the VSTOR pin voltage remains above the internal under voltage threshold (VBAT_UV) for the additional 64 ms after the VRDIV initialization pulse (following the 45-ms PFET on time), the internal PFET turns back on and the main boost charger begins to charge the storage element assuming there is sufficient power available from the harvester at the VIN_DC pin. If VSTOR does not reach the VBAT_UV threshold, then the PFET remains off until the main boost charger can raise the VSTOR voltage to VBAT_UV. If a system load tied to VSTOR discharges VSTOR below VSTOR_GEN or below VBAT_UV during the 32 ms initial MPPT reference voltage measurement or within 110 ms after hot plug, it is recommended to add an external PFET between the system load and VSTOR. An inverted VBAT_OK signal can be used to drive the gate of this system-isolating, external PFET. Otherwise, the VSTOR voltage waveform will have incremental pulses as the IC turns on and off the internal PFET controlled by VBAT_UV or cycles between cold-start and main boost charger operation.

Once VSTOR is above VSTOR_CHGEN, the main boost charger employs pulse frequency modulation (PFM) mode of control to regulate the voltage at VIN_DC close to the desired reference voltage. The reference voltage is set by the MPPT control scheme as described in the features section. Input voltage regulation is obtained by transferring charge from the input to VSTOR only when the input voltage is higher than the voltage on pin VREF_SAMP. The current through the inductor is controlled through internal current sense circuitry. The peak current in the inductor is dithered internally to up to three pre-determined levels in order to maintain high efficiency of the charger across a wide input current range. The charger transfers up to a maximum of 100 mA average input current (230mA typical peak inductor current). The boost charger is disabled when the voltage on VSTOR reaches the user set VBAT_OV threshold to protect the battery connected at VBAT from overcharging. In order for the battery to charge to VBAT_OV, the input power must exceed the power needed for the load on VSTOR. See the *节 10* section for guidance on minimum input power requirements.

Steady state operation for the boost charger is shown in 图 9-3. These plots highlight the inductor current, the VSTOR voltage ripple, input voltage regulation and the LBOOST switching node. The cycle-by-cycle minor switching frequency is a function of the boost converter's inductor value, peak current limit and voltage levels on each side of each inductor. Once the VSTOR capacitor, CSTOR, droops below a minimum value, the hysteretic switching repeats.

CAUTION

If VIN_DC is higher than VSTOR and VSTOR is higher than VBAT_OV, the input VIN_DC is pulled to ground through a small resistance to stop further charging of the attached battery or capacitor. It is critical that if this case is expected, the impedance of the source attached to VIN_DC be higher than 20 Ω and not a low impedance source.

8.4.3 Thermal Shutdown

Rechargeable Li-ion batteries need protection from damage due to operation at elevated temperatures. The application should provide this battery protection and ensure that the ambient temperature is never elevated greater than the expected operational range of 85°C.

The BQ25504 uses an integrated temperature sensor to monitor the junction temperature of the device. If the OT_PROG pin is tied low, then the temperature threshold for thermal protection is set to TSD_ProtL which is 65°C typically. If the OT_PROG is tied high, then the temperature is set to TSD_ProtH which is 120°C typically. Once the temperature threshold is exceeded, the boost converter/charger is disabled and charging ceases. Once the temperature of the device drops below this threshold, the boost converter and or charger can resume operation. To avoid unstable operation near the overtemp threshold, a built-in hysteresis of approximately 5°C has been implemented. Care should be taken to not over discharge the battery in this condition since the boost

converter/charger is disabled. However, if the supply voltage drops to the VBAT_UV setting, then the switch between VBAT and VSTOR will open and protect the battery even if the device is in thermal shutdown.

9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Application Information

9.1.1 Storage Element Selection

In order for the charge management circuitry to protect the storage element from over-charging or discharging, the storage element must be connected to VBAT pin and the system load tied to the VSTOR pin. Many types of elements can be used, such as capacitors, super capacitors or various battery chemistries. A storage element with 100 uF equivalent capacitance is required to filter the pulse currents of the PFM switching charger. The equivalent capacitance of a battery can be computed as computed as:

$$C_{EQ} = 2 \times mAHr_{BAT(CHRGD)} \times 3600\ s/Hr / V_{BAT(CHRGD)} \quad (6)$$

In order for the storage element to be able to charge VSTOR capacitor (CSTOR) within the $t_{VB\_HOT\_PLUG}$ (50 ms typical) window at hot-plug; therefore preventing the IC from entering cold start, the time constant created by the storage element's series resistance (plus the resistance of the internal PFET switch) and equivalent capacitance must be less than $t_{VB\_HOT\_PLUG}$. For example, a battery's resistance can be computed as:

$$R_{BAT} = V_{BAT} / I_{BAT(CONTINUOUS)} \text{ from the battery specifications.} \quad (7)$$

The storage element must be sized large enough to provide all of the system load during periods when the harvester is no longer providing power. The harvester is expected to provide at least enough power to fully charge the storage element while the system is in low power or sleep mode. Assuming no load on VSTOR (i.e., the system is in low power or sleep mode), the following equation estimates charge time from voltage VBAT1 to VBAT2 for given input power is:

Refer to SLUC462 for a design example that sizes the storage element.

$$PIN \times \eta_{EST} \times t_{CHRG} = 1/2 \times CEQ \times (VBAT2^2 - VBAT1^2) \quad (8)$$

Note that if there are large load transients or the storage element has significant impedance then it may be necessary to increase the CSTOR capacitor from the 4.7uF minimum or add additional capacitance to VBAT in order to prevent a droop in the VSTOR voltage. See below for guidance on sizing capacitors.

9.1.2 Inductor Selection

The boost charger needs an appropriately sized inductor for proper operation. The inductor's saturation current should be at least 25% higher than the expected peak inductor currents recommended below if system load transients on VSTOR are expected. Since this device uses hysteretic control, the boost charger is considered naturally stable systems (single order transfer function).

For the boost charger to operate properly, an inductor of appropriate value must be connected between LBOOST, pin 20, and VIN_DC, pin 2. The boost charger internal control circuitry is designed to control the switching behavior with a nominal inductance of 22 µH ± 20%. The inductor must have a peak current capability of > 300 mA with a low series resistance (DCR) to maintain high efficiency.

A list of inductors recommended for this device is shown in 表 9-1.

表 9-1. Recommended Inductors

INDUCTANCE (µH)	DIMENSIONS (mm)	PART NUMBER	MANUFACTURER(1)
22	4.0x4.0x1.7	LPS4018-223M	Coilcraft
22	3.8x3.8x1.65	744031220	Wurth

表 9-1. Recommended Inductors (continued)

INDUCTANCE (µH)	DIMENSIONS (mm)	PART NUMBER	MANUFACTURER(1)
22	2.8x2.8x2.8	744025220	Wurth

(1) See **WHAT?** concerning recommended third-party products.

9.1.3 Capacitor Selection

In general, all the capacitors need to be low leakage. Any leakage the capacitors have will reduce efficiency, increase the quiescent current and diminish the effectiveness of the IC for energy harvesting.

9.1.3.1 VREF_SAMP Capacitance

The MPPT operation depends on the sampled value of the open circuit voltage and the input regulation follows the voltage stored on the CREF capacitor. This capacitor is sensitive to leakage since the holding period is around 16 seconds. As the capacitor voltage drops due to any leakage, the input regulation voltage also drops preventing proper operation from extraction the maximum power from the input source. Therefore, it is recommended that the capacitor be an X7R or COG low leakage capacitor.

9.1.3.2 VIN_DC Capacitance

Energy from the energy harvester input source is initially stored on a capacitor, CIN, connected to VIN_DC, pin 2, and VSS, pin 1. For energy harvesters which have a source impedance which is dominated by a capacitive behavior, the value of the harvester capacitor should scaled according to the value of the output capacitance of the energy source, but a minimum value of 4.7 µF is recommended.

9.1.3.3 VSTOR Capacitance

Operation of the BQ25504 requires two capacitors to be connected between VSTOR, pin 15, and VSS, pin 1. A high frequency bypass capacitor of at 0.1 µF should be placed as close as possible between VSTOR and VSS. In addition, a low ESR capacitor of at least 4.7 µF should be connected in parallel.

9.1.3.4 Additional Capacitance on VSTOR or VBAT

If there are large, fast system load transients and/or the storage element has high resistance, then the CSTOR capacitors may momentarily discharge below the VBAT_UV threshold in response to the transient. This causes the BQ25504 to turn off the PFET switch between VSTOR and VBAT and turn on the boost charger. The CSTOR capacitors may further discharge below the VSTOR_CHGEN threshold and cause the BQ25504 to enter Cold Start. For instance, some Li-ion batteries or thin-film batteries may not have the current capacity to meet the surge current requirements of an attached low power radio. To prevent VSTOR from drooping, either increasing the CSTOR capacitance or adding additional capacitance in parallel with the storage element is recommended. For example, if boost charger is configured to charge the storage element to 4.2 V and a 500 mA load transient of 50 µs duration infrequently occurs, then, solving I = C x dv/dt for CSTOR gives:

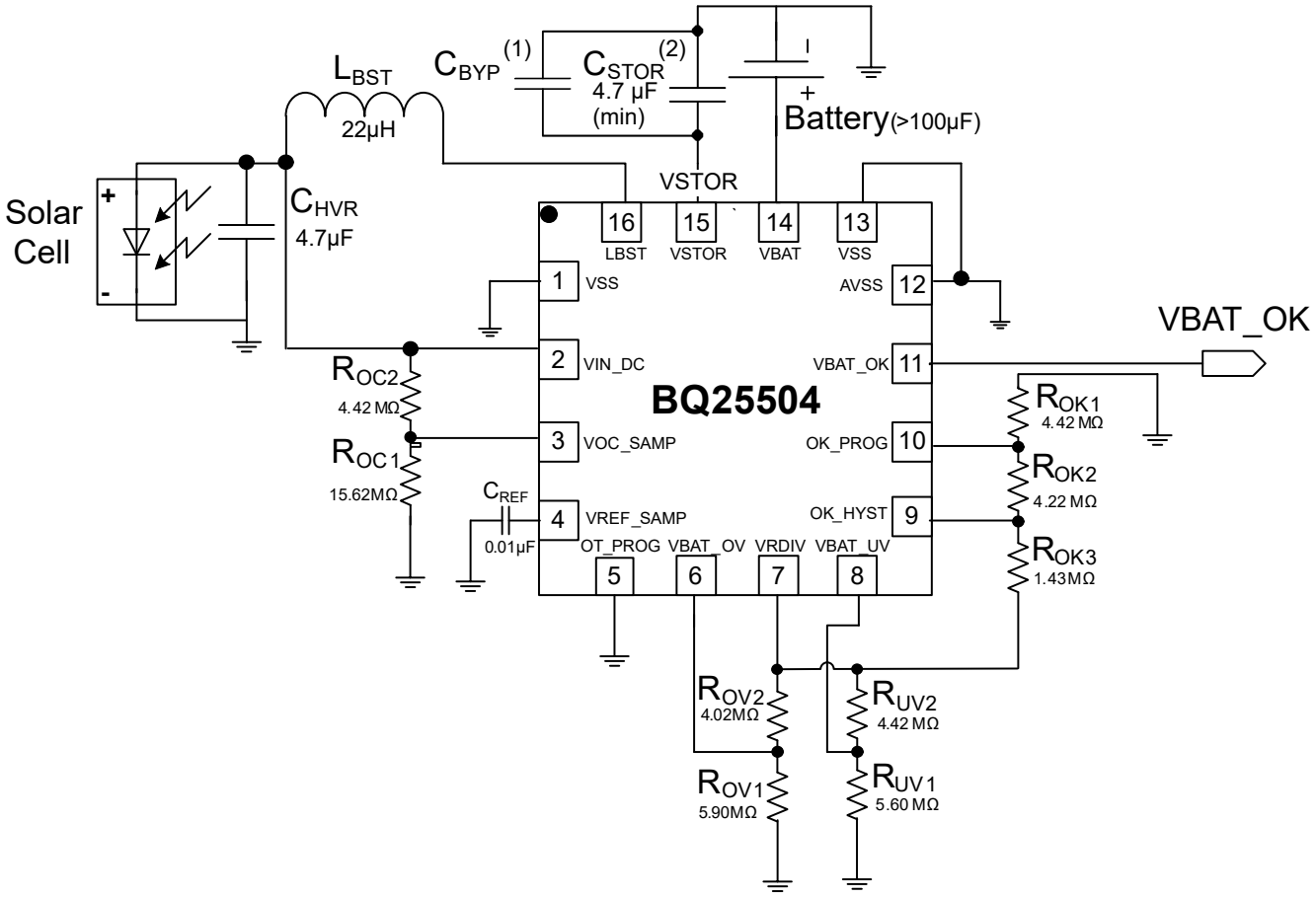
$$\text{CSTOR} \geq \frac{500\ \text{mA} \times 50\ \mu\text{s}}{(4.2\ \text{V} - 1.8\ \text{V})} = 10.5\ \mu\text{F} \tag{9}$$

Note that increasing CSTOR is the recommended solution but will cause the boost charger to operate in the less efficient cold start mode for a longer period at startup compared to using CSTOR = 4.7 µF. If longer cold start run times are not acceptable, then place the additional capacitance in parallel with the storage element.

For a recommended list of standard components, see the EVM User’s Guide (SLUUAA8).

9.2 Typical Applications

9.2.1 Solar Application Circuit



A. Place close as possible to IC pin 15 (VSTOR) and pin 13 (VSS)

B. See the Capacitor Selection section for guidance on sizing C_{STOR}

图 9-1. Typical Solar Application Circuit

9.2.1.1 Design Requirements

The desired voltage levels are VBAT_OV = 3.15 V, VBAT_UV = 2.20 V, VBAT_OK = 2.44 V, VBAT_OK_HYST = 2.80 V and MPP (V_{OC}) = 78% which is typical for solar panels. There are no large load transients expected. The IC must stop charging if its junction temperature is above 65°C. The simulated solar panel open circuit voltage is 1.0 V.

9.2.1.2 Detailed Design Procedure

The recommended L1 = 22 µH, C_{BYP} = 0.01 µF and low leakage CREF = 10 nF are selected. In order to ensure the fastest recovery of the harvester output voltage to the MPPT level following power extraction, the minimum recommended CIN = 4.7 µF is selected. Because no large system load transients are expected and to ensure fast charge time during cold start, the minimum recommended CSTOR = 4.7 µF. To stop charging when the IC junction temperature is above 65°C, the OT_PROG pin is tied to ground.

- With VBAT_UV < VBAT_OV ⩽ 5.5 V, to size the VBAT_OV resistors, first choose $RSUM_{OV} = R_{OV1} + R_{OV2}$ = 10 MΩ then solve Equation 3 for

$$R_{OV1} = \frac{3}{2} \times \frac{RSUM_{OV} \times VBIAS}{VBAT\_OV} \times \frac{3}{2} \frac{10\ M\Omega \times 1.25\ V}{3.15\ V} = 5.95\ M\Omega \rightarrow 5.90\ M\Omega \text{ closest 1\% value then} \quad (10)$$

- $R_{OV2} = RSUM_{OV} - R_{OV1} = 10\ M\Omega - 5.95\ M\Omega = 4.05\ M\Omega \rightarrow 4.02\ M\Omega$ resulting in VBAT_OV = 3.15 V
- To size the VBAT_UV resistors, first choose $RSUM_{UV} = R_{UV1} + R_{UV2} = 10\ M\Omega$ then solve 方程式 2 for

$$R_{UV1} = \frac{RSUM_{UV} \times VBIAS}{VBAT_{UV}} = \frac{10\ M\Omega \times 1.25\ V}{2.2\ V} = 5.68\ M\Omega \rightarrow 5.60\ M\Omega \text{ closest 1\% value then} \quad (11)$$

- $R_{UV2} = RSUM_{UV} - R_{UV1} = 10\ M\Omega - 5.60\ M\Omega = 4.4\ M\Omega \rightarrow 4.42\ M\Omega$ closest 1% resistor resulting in VBAT_UV = 2.2 V.
- With VBAT_OV ⩾ VBAT_OK_HYST > VBAT_OK ⩾ VBAT_UV, to size the VBAT_OK and VBAT_OK_HYST resistors,
  first choose $RSUM_{OK} = R_{OK1} + R_{OK2} + R_{OK3} = 10\ M\Omega$ then solve Equation 4 and Equation 5 for

$$R_{OK1} = \frac{VBIAS \times RSUM_{OK}}{VBAT\_OK\_HYST} = \left(\frac{1.25\ V}{2.8\ V}\right) \times 10\ M\Omega = 4.46\ M\Omega \rightarrow 4.42\ M\Omega \text{ closest 1\% resistor then} \quad (12)$$

$$R_{OK2} = \left(\frac{VBAT\_OK\_PROG}{VBIAS} - 1\right) \times R_{OK1} = \left(\frac{2.45\ V}{1.25\ V} - 1\right) \times 4.24\ M\Omega = 4.07\ M\Omega, \text{ then} \quad (13)$$

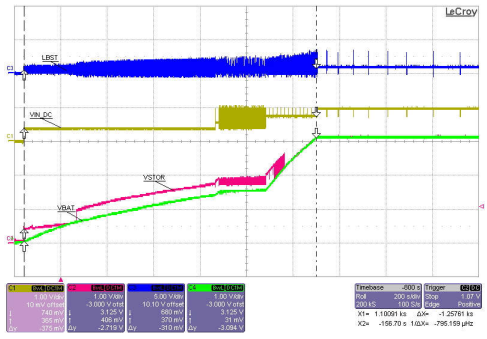
- $R_{OK3} = RSUM_{OK} - R_{OK1} - R_{OK2} = 10\ M\Omega - 4.42\ M\Omega - 4.22\ M\Omega = 1.36\ M\Omega \rightarrow 1.43\ M\Omega$ to give VBAT_OK = 2.44 V and VBAT_OK_HYST = 2.85 V.
- Keeping in mind that VREF_SAMP stores the MPP voltage for the harvester, first choose $RSUM_{OC} = R_{OC1} + R_{OC2} = 20\ M\Omega$ then solve Equation 1 for

$$R_{OC1} = \left(\frac{VREF\_SAMP}{VIN\_DC(OC)}\right) \times RSUM_{OC} = 0.78 \times 20\ M\Omega = 15.6\ M\Omega, \text{ then} \quad (14)$$

$$R_{OC2} = RSUM_{OC} \times \left(1 - \frac{VREF\_SAMP}{VIN\_DC(OC)}\right) = 20\ M\Omega(1 - 0.78) = 4.4\ M\Omega \text{ closest 1\% resistors} \quad (15)$$

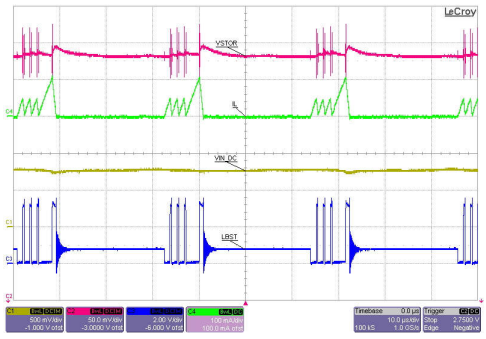
- SLURAQ1 provides help on sizing and selecting the resistors.

9.2.1.3 Application Curves



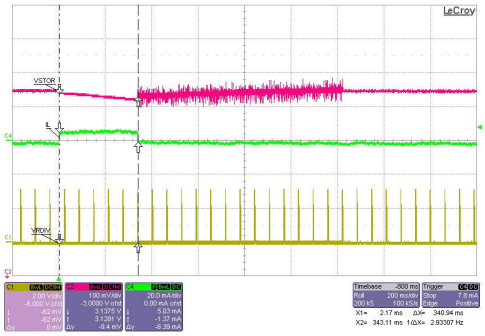
VINDC = sourcemeter with V_{SOURCE} = 1.0 V and compliance of 2.75 mA
VBAT connected to 0.1 F depleted supercap
No resistance load on VSTOR

图 9-2. Startup into Depleted Storage Element



VIN_DC = sourcemeter with V_{SOURCE} = 1 V and compliance of 10.5 mA
VBAT = 0.1 F supercap
VSTOR = 2 kΩ resistive load

图 9-3. Boost Charger Operational Waveforms

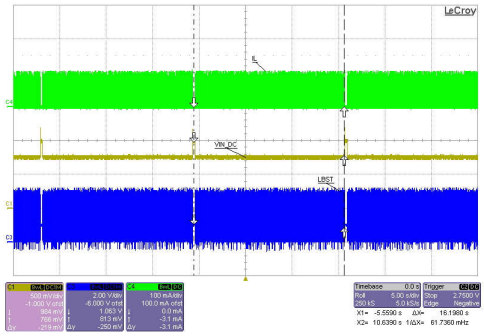


VIN_DC = sourcemeter with V_{SOURCE} = 1 V and compliance of 10.5 mA

VBAT = 0.1 F supercap

VSTOR = open to 500 Ω to open resistive load (IL = load current on VSTOR)

图 9-4. 5 mA Load Transient on VSTOR

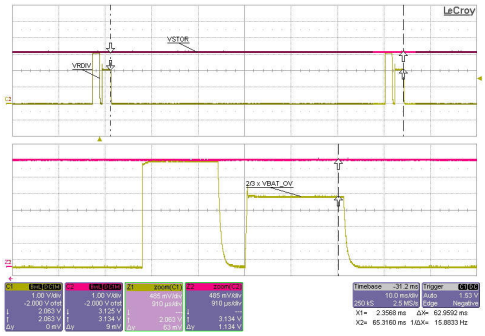


VIN_DC = sourcemeter with V_{SOURCE} = 1 V and compliance of 10.5 mA

VBAT = sourcemeter with V_{SOURCE} = 2.8V and compliance of 1A

IL = inductor current

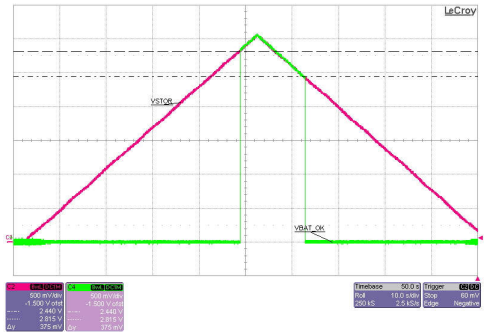
图 9-5. MPPT Operation



VIN_DC = sourcemeter with V_{SOURCE} = 1 V and compliance of 10.5 mA

VBAT = sourcemeter with V_{SOURCE} = 2.8 V and compliance of 1A

图 9-6. VRDIV Operation



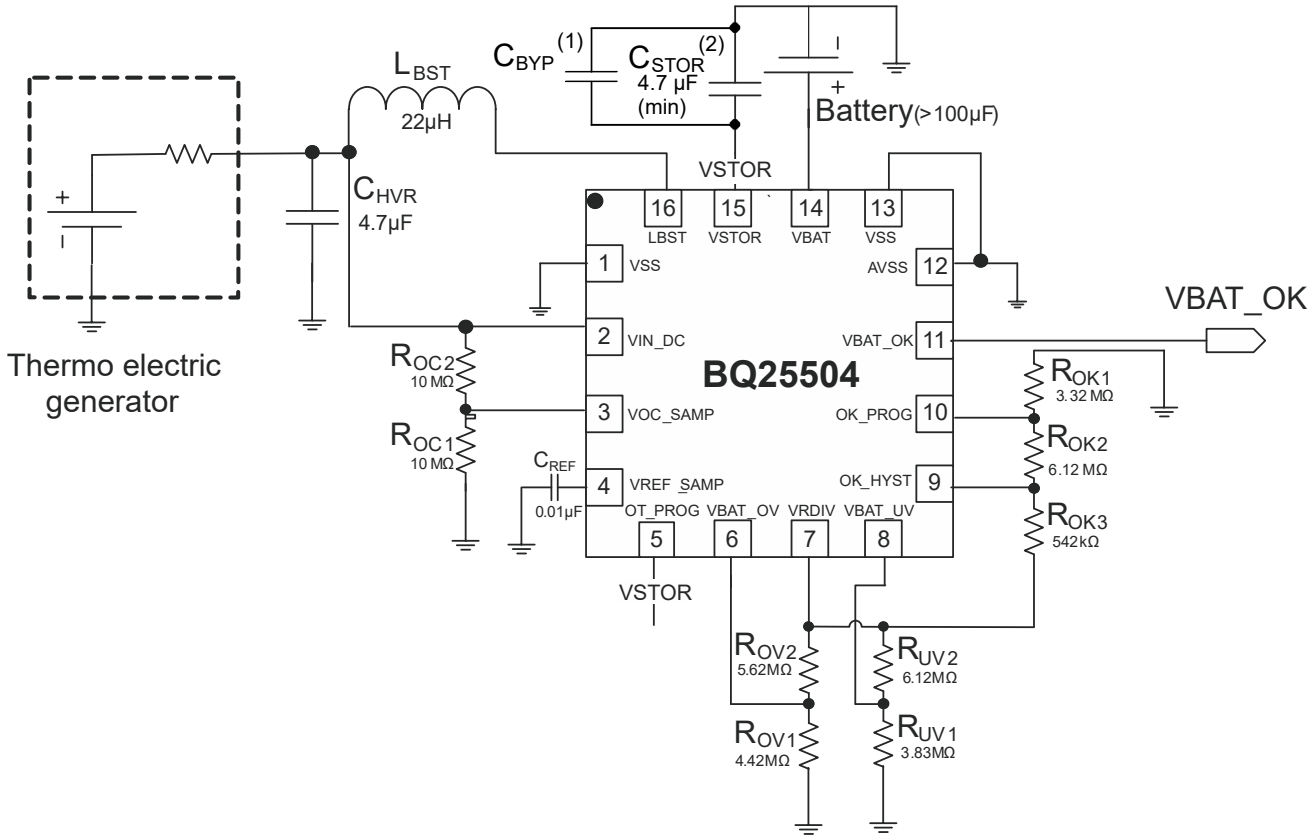
VIN_DC = sourcemeter with V_{SOURCE} = 1 V and compliance of 2.75 mA

No storage element on VBAT

VSTOR artificially ramped from 0V to 3.15 V to 0 V using a power amp driven by a function generator

图 9-7. VBAT_OK Operation

9.2.2 TEG Application Circuit



A. Place close as possible to IC pin 15 (VSTOR) and pin 13 (VSS)
B. See the Capacitor Selection section for guidance on sizing C_{STOR}

图 9-8. Typical TEG Application Circuit

9.2.2.1 Design Requirements

The desired voltage levels are VBAT_OV = 4.25 V, VBAT_UV = 3.20 V, VBAT_OK = 3.55 V, VBAT_OK_HYST = 3.76 V and MPP (V_{OC}) = 50% which is typical for TEG harvesters. The IC must stop charging if its junction temperature is above 120°C. The simulated TEG open circuit voltage is 1.0 V.

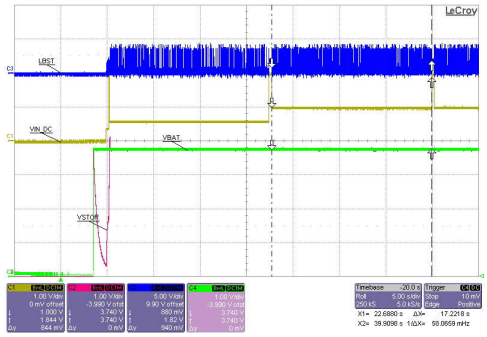
9.2.2.2 Detailed Design Procedure

The recommended L1 = 22 µH, C_{BYP} = 0.01 µF and low leakage CREF = 10 nF are selected. In order to ensure the fastest recovery of the harvester output voltage to the MPPT level following power extraction, the minimum recommended CIN = 4.7 µF is selected. Because no large system load transients are expected and to ensure fast charge time during cold start, the minimum recommended CSTOR = 4.7 µF. To stop charging when the IC junction temperature is above 120°C, the OT_PROG pin is tied to VSTOR.

Referring back to the procedure in 节 *9.2.1.2* or using the spreadsheet calculator at SLURAQ1 gives the following values:

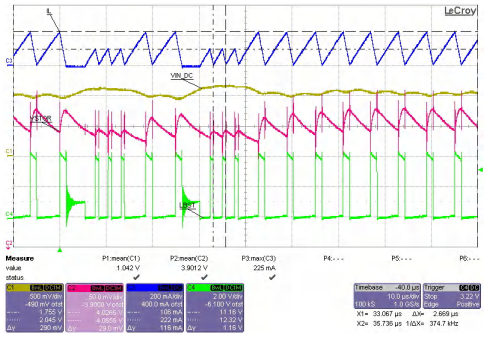
- R_{OV1} = 4.42 MΩ, R_{OV2} = 5.49 MΩ resulting in VBAT_OV = 4.26 V due to rounding to the nearest 1% resistor.
- R_{UV1} = 3.83 MΩ, R_{UV2} = 6.04 MΩ resulting in VBAT_UV = 3.22 V due to rounding to the nearest 1% resistor
- R_{OK1} = 3.32 MΩ, R_{OK2} = 6.04 MΩ, R_{OK3} = 0.536 MΩ resulting in VBAT_OK = 3.52 V and VBAT_OK_HYST = 3.73 V after rounding.
- R_{OC1} = 10 MΩ and R_{OC2} = 10 MΩ gives 50% MPP voltage.

9.2.2.3 Application Curves



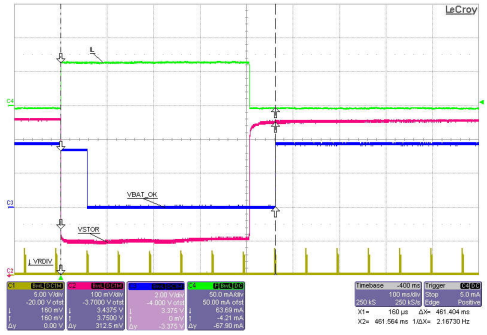
VINDC = sourcemeter with V_{SOURCE} = 2.0 V and compliance of 1 mA
VBAT connected to LiIon battery
VSTOR = 50 kΩ resistor

图 9-9. Startup by Attaching Charged Storage Element



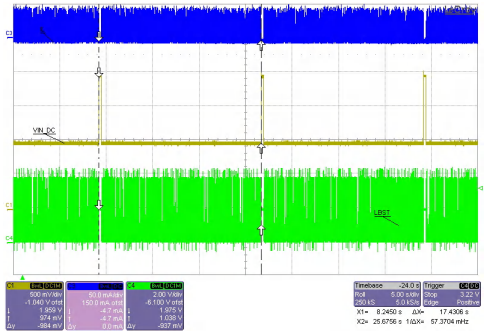
VIN_DC = sourcemeter with V_{SOURCE} = 2.0 V and compliance of 100 mA
VBAT connected to LiIon battery
VSTOR = 100 kΩ resistive load (IL = inductor current)

图 9-10. Boost Charger Operational Waveforms



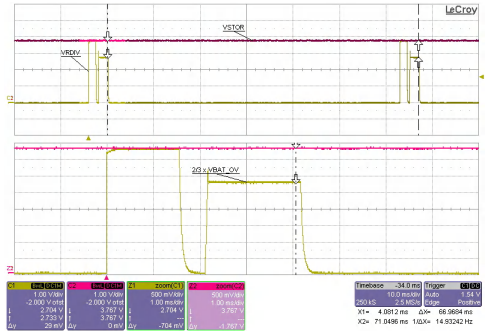
VIN_DC = sourcemeter with V_{SOURCE} = 2.0 V and compliance of 1 mA
VBAT connected to LiIon battery
VSTOR = open to 50 Ω to open resistive load (IL = load current on VSTOR)

图 9-11. 50 mA Load Transient on VSTOR



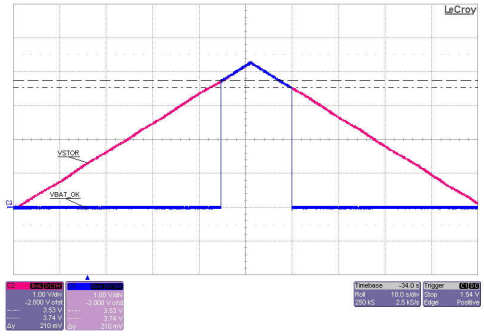
VIN_DC = sourcemeter with V_{SOURCE} = 2.0 V and compliance of 1 mA
VBAT connected to LiIon battery
IL = inductor current

图 9-12. MPPT Operation



VIN_DC = sourcemeter with V_{SOURCE} = 2.0 V and compliance of 1 mA
VBAT connected to LiIon battery

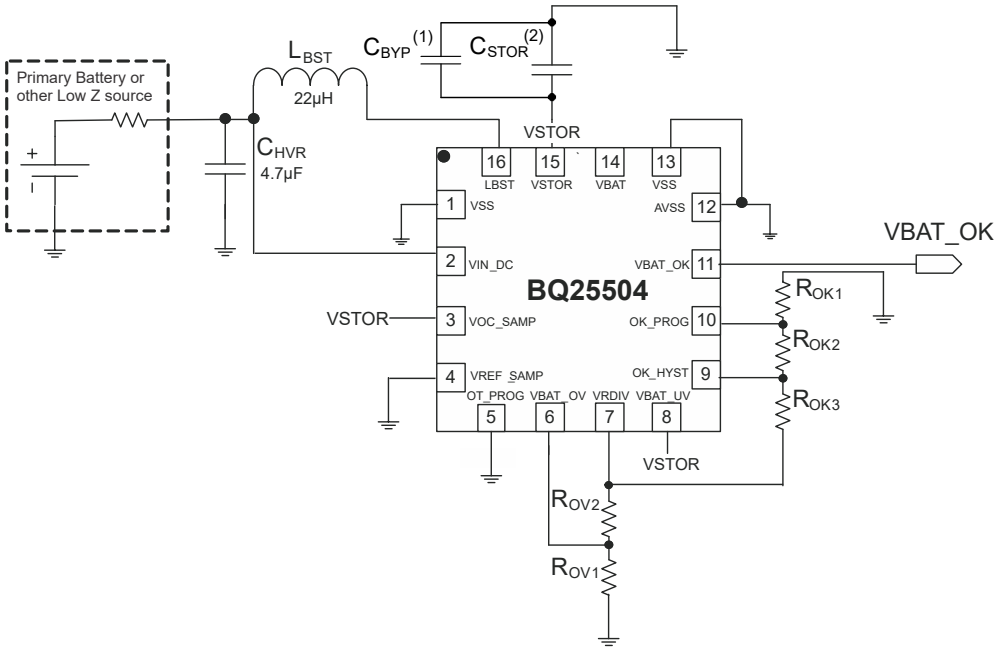
图 9-13. VRDIV Operation



VIN_DC = sourcemeter with V_{SOURCE} = 2.0 V and compliance of 1 mA
No storage element on VBAT
VSTOR artificially ramped from 0V to 4.25V to 0V using a power amp driven by a function generator

图 9-14. VBAT_OK Operation

9.2.3 MPPT Disabled, Low Impedance Source Application Circuit



A. Place close as possible to IC pin 15 (VSTOR) and pin 13 (VSS)
B. See the Capacitor Selection section for guidance on sizing C_{STOR}

图 9-15. Typical MPPT Disabled Application Circuit (Low Iq Boost Converter from Low Impedance Source)

9.2.3.1 Design Requirements

The input source is a low impedance 1.2 V battery therefore MPPT is not needed. The output will be a low ESR capacitor therefore VSTOR can be tied to VBAT and VBAT_UV is not needed. The desired voltage levels are VBAT_OV = 3.30 V, VBAT_OK = 2.80 V, VBAT_OK_HYST = 3.10 V, and MPPT disabled. The IC must stop charging if its junction temperature is above 65°C. Load transients are expected.

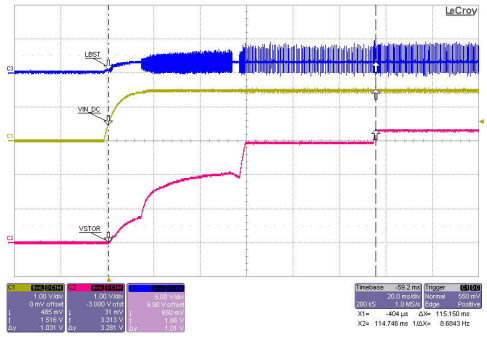
9.2.3.2 Detailed Design Procedure

The recommended L1 = 22 µH, C_{BYP} = 0.01 µF and low leakage CREF = 10 nF are selected. The minimum recommended CIN = 4.7 µF is selected. To prevent VSTOR from drooping during system load transients, CSTOR is set to 100 µF. To disable the sampling for MPPT, the VOC_SAMP pin is tied to VSTOR. To disable the input voltage regulation circuit, the VREF_SAMP pin is tied to GND. Since the VBAT_UV function is not needed, the VBAT_UV can be tied to VSTOR. To stop charging when the IC junction temperature is above 65°C, the OT_PROG pin is tied to GND.

Referring back to the procedure in *节 9.2.1.2* or using the spreadsheet calculator at SLURAQ1 gives the following values:

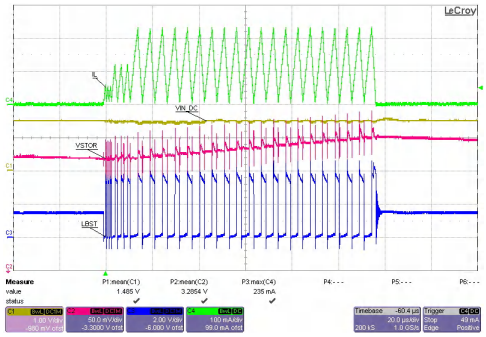
- R_{OV1} = 5.62 MΩ, R_{OV2} = 4.22 MΩ resulting in VBAT_OV = 3.28 V due to rounding to the nearest 1% resistor.
- R_{OK1} = 4.12 MΩ, R_{OK2} = 5.11 MΩ, R_{OK3} = 0.976 MΩ resulting in VBAT_OK = 2.80 V and VBAT_OK_HYST = 3.10 V after rounding.

9.2.3.3 Application Curves



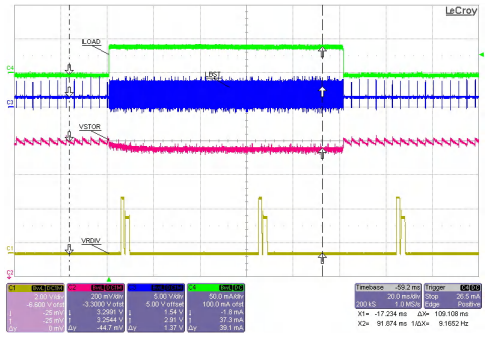
VIN_DC = low impedance voltage source = 1.5 V
VBAT = VSTOR = 100 µF
VSTOR = 500 Ω resistor

图 9-16. Startup



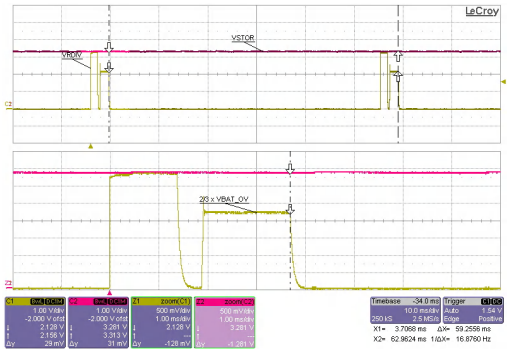
VIN_DC = low impedance voltage source = 1.5 V
VBAT = VSTOR = 100 µF
VSTOR = 330 Ω resistive load (IL = inductor current)

图 9-17. Boost Charger Operational Waveforms



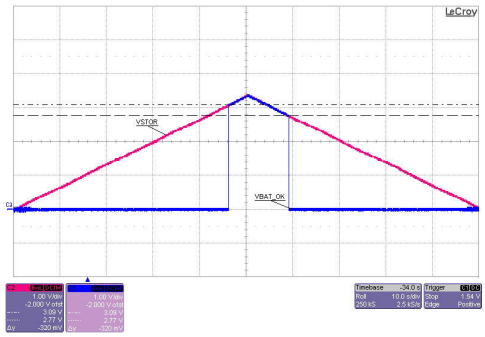
VIN_DC = low impedance voltage source = 1.5 V)
VBAT = VSTOR = 100 µF
VSTOR = open to 75 Ω to open resistive load (IL = load current on VSTOR

图 9-18. 40 mA Load Transient on VSTOR



VIN_DC = low impedance voltage source = 1.5 V
VBAT = VSTOR = 100 µF

图 9-19. VRDIV Operation



VIN_DC = low impedance voltage source = 1.5 V
VBAT = VSTOR = 100 µF
VSTOR artificially ramped from 0 V to 3.3 V to 0 V using a power amp driven by a function generator

图 9-20. VBAT_OK Operation

10 Power Supply Recommendations

The energy harvesting source (e.g., solar panel, TEG, vibration element) must provide a minimum level of power for the IC to operate as designed. The IC's minimum input power required to exit cold start can be estimated as:

$$PIN > PIN(CS) = VIN(CS) \times IIN(CS) > \frac{\left(I - STR\_ELM\_LEAK_{@1.8V} \times 1.8V\right) + \frac{(1.8V)^2}{RSTOR(CS)}}{0.05} \quad (16)$$

where I-STR_ELM_LEAK$_{@1.8V}$ is the storage element leakage current at 1.8V and

RSTOR(CS) is the equivalent resistive load on VSTOR during cold start and 0.05 is an estimate of the worst case efficiency of the cold start circuit.

Once the IC is out of cold start and the system load has been activated (e.g., using the VBAT_OK signal), the energy harvesting element must provide the main boost charger with at least enough power to meet the average system load. Assuming RSTOR(AVG) represents the average resistive load on VSTOR, the simplified **equation below** gives an estimate of the IC's minimum input power needed during system operation:

$$PIN \times \eta_{EST} > PLOAD = \frac{(VBAT\_OV)^2}{RSTOR(AVG)} + VBAT\_OV \times I - STR\_ELM\_LEAK_{@VBAT\_OV} \quad (17)$$

where η_{EST} can be derived from the datasheet efficiency curves for the given input voltage and current and VBAT_OV. The simplified equation above assumes that, while the harvester is still providing power, the system goes into low power or sleep mode long enough to charge the storage element so that it can power the system when the harvester eventually is down. Refer to spreadsheet SLUC462 for a design example that sizes the energy harvester.

11 Layout

11.1 Layout Guidelines

As for all switching power supplies, the PCB layout is an important step in the design, especially at high peak currents and high switching frequencies. If the layout is not carefully done, the boost charger could show stability problems as well as EMI problems. Therefore, use wide and short traces for the main current path and for the power ground paths. The input and output capacitors as well as the inductors should be placed as close as possible to the IC. For the boost charger, first priority are the output capacitors, including the 0.1 uF bypass capacitor (CBYP), followed by CSTOR, which should be placed as close as possible between VSTOR, pin 15, and VSS, pin 1 or 13. Next, the input capacitor, CIN, should be placed as close as possible between VIN_DC, pin 2, and VSS, pin 1. Last in priority is the boost charger inductor, L1, which should be placed close to LBOOST, pin 16, and VIN_DC, pin 2 if possible. It is best to use vias and bottom traces for connecting the inductor to its respective pins instead of the capacitors.

To minimize noise pickup by the high impedance voltage setting nodes (VBAT_OV, VBAT_UV, OK_PROG, OK_HYST), the external resistors should be placed so that the traces connecting the midpoints of each divider to their respective pins are as short as possible. When laying out the non-power ground return paths (e.g. from resistors and CREF), it is recommended to use short traces as well, separated from the power ground traces and connected to AVSS pin 12. This avoids ground shift problems, which can occur due to superimposition of power ground current and control ground current. The PowerPad should not be used as a power ground return path.

The remaining pins are digital signals with minimal layout restrictions. See 图 11-1 for an example layout.

In order to maximize efficiency at light load, the use of voltage level setting resistors > 1 MΩ is recommended. In addition, the sample and hold circuit output capacitor on VREF_SAMP must hold the voltage for 16 s. During board assembly, contaminants such as solder flux and even some board cleaning agents can leave residue that may form parasitic resistors across the physical resistors/capacitors and/or from one end of a resistor/capacitor to ground, especially in humid, fast airflow environments. This can result in the voltage regulation and threshold levels changing significantly from those expected per the installed components. Therefore, it is highly recommended that no ground planes be poured near the voltage setting resistors or the sample and hold capacitor. In addition, the boards must be carefully cleaned, possibly rotated at least once during cleaning, and then rinsed with de-ionized water until the ionic contamination of that water is well above 50 Mohm. If this is not feasible, then it is recommended that the sum of the voltage setting resistors be reduced to at least 5X below the measured ionic contamination.

11.2 Layout Example

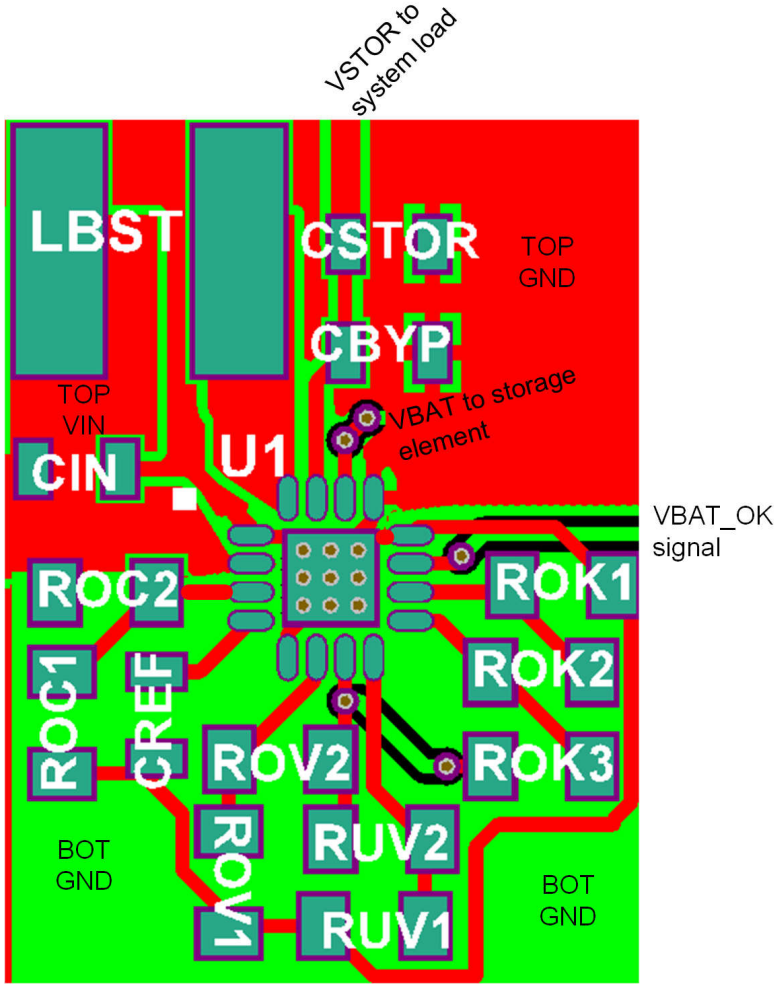


图 11-1. Recommended Layout

11.3 Thermal Considerations

Implementation of integrated circuits in low-profile and fine-pitch surface-mount packages typically requires special attention to power dissipation. Many system-dependent issues such as thermal coupling, airflow, added heat sinks and convection surfaces, and the presence of other heat-generating components affect the power-dissipation limits of a given component.

Three basic approaches for enhancing thermal performance are listed below.

- Improving the power-dissipation capability of the PCB design
- Improving the thermal coupling of the component to the PCB
- Introducing airflow in the system

For more details on how to use the thermal parameters in the Thermal Table, check the Thermal Characteristics Application Note (SZZA017) and the IC Package Thermal Metrics Application Note (SPRA953).

12 Device and Documentation Support

12.1 Device Support

12.1.1 第三方产品免责声明

TI 发布的与第三方产品或服务有关的信息，不能构成与此类产品或服务或保修的适用性有关的认可，不能构成此类产品或服务单独或与任何 TI 产品或服务一起的表示或认可。

12.1.2 Zip Files

- http://www.ti.com/lit/zip/SLUC484
- http://www.ti.com/lit/zip/SLURAQ1
- http://www.ti.com/lit/zip/SLUC462

12.2 Documentation Support

12.2.1 Related Documentation

For related documentation see the following:

- EVM User’s Guide, SLUUAA8
- Thermal Characteristics Application Note, SZZA017
- IC Package Thermal Metrics Application Note, SPRA953

12.3 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.4 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

12.5 Trademarks

TI E2E™ is a trademark of Texas Instruments.
所有商标均为其各自所有者的财产。

12.6 静电放电警告

静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.7 术语表

TI 术语表	本术语表列出并解释了术语、首字母缩略词和定义。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
BQ25504RGTR	Active	Production	VQFN (RGT) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	B5504
BQ25504RGTR.B	Active	Production	VQFN (RGT) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	B5504
BQ25504RGTT	Active	Production	VQFN (RGT) | 16	250 | SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	B5504
BQ25504RGTT.B	Active	Production	VQFN (RGT) | 16	250 | SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	B5504

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

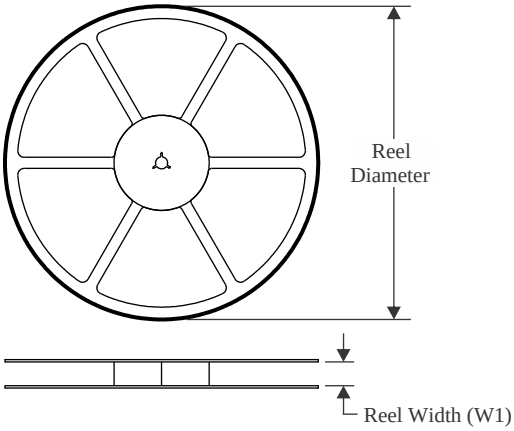
(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

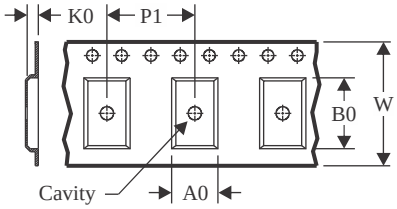
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

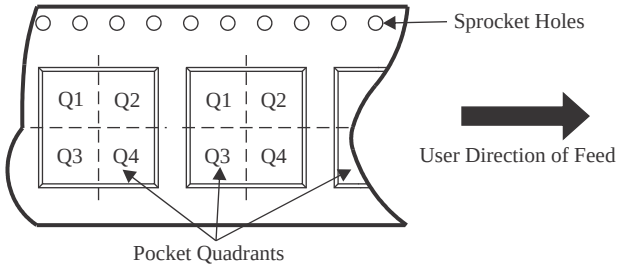


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

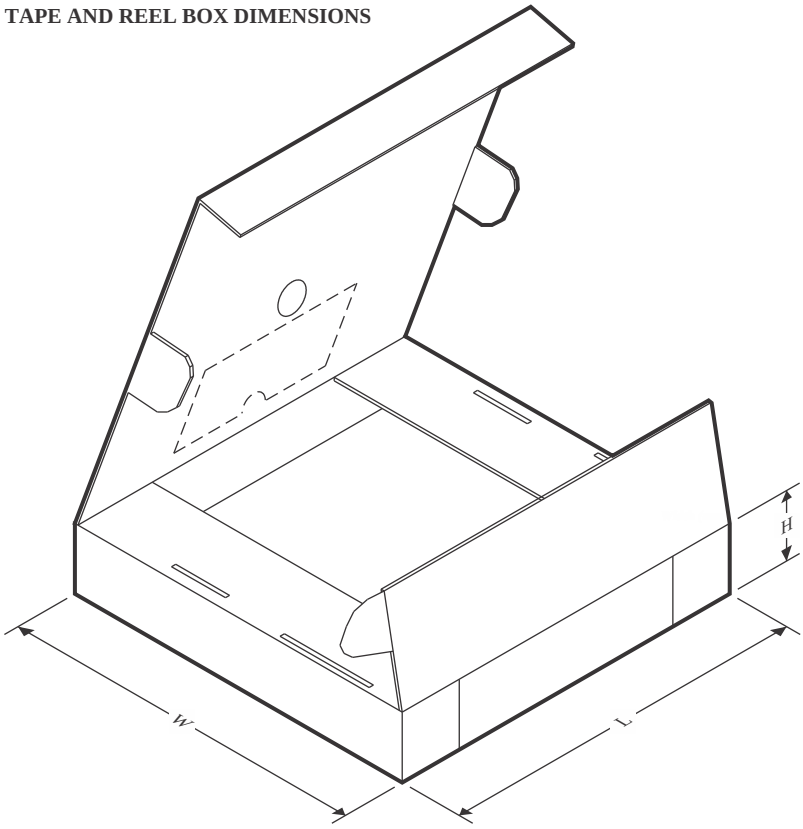
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ25504RGTR	VQFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
BQ25504RGTT	VQFN	RGT	16	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS

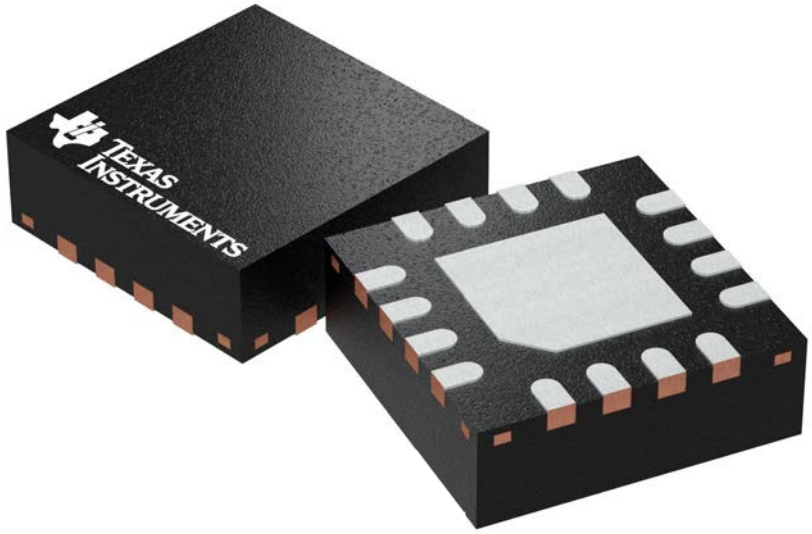


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ25504RGTR	VQFN	RGT	16	3000	346.0	346.0	33.0
BQ25504RGTT	VQFN	RGT	16	250	210.0	185.0	35.0

RGT 16 VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



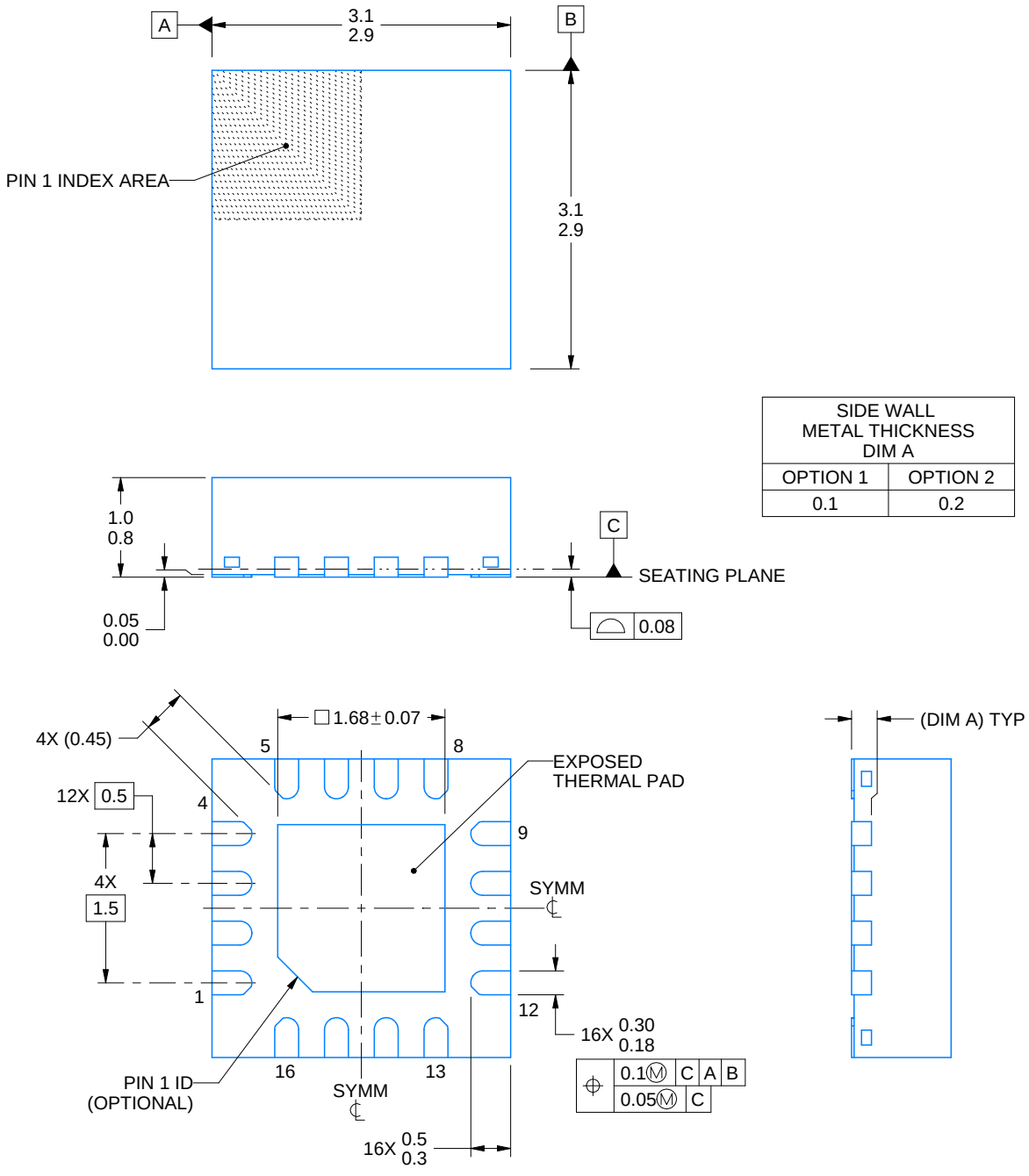
Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

PACKAGE OUTLINE

RGT0016C

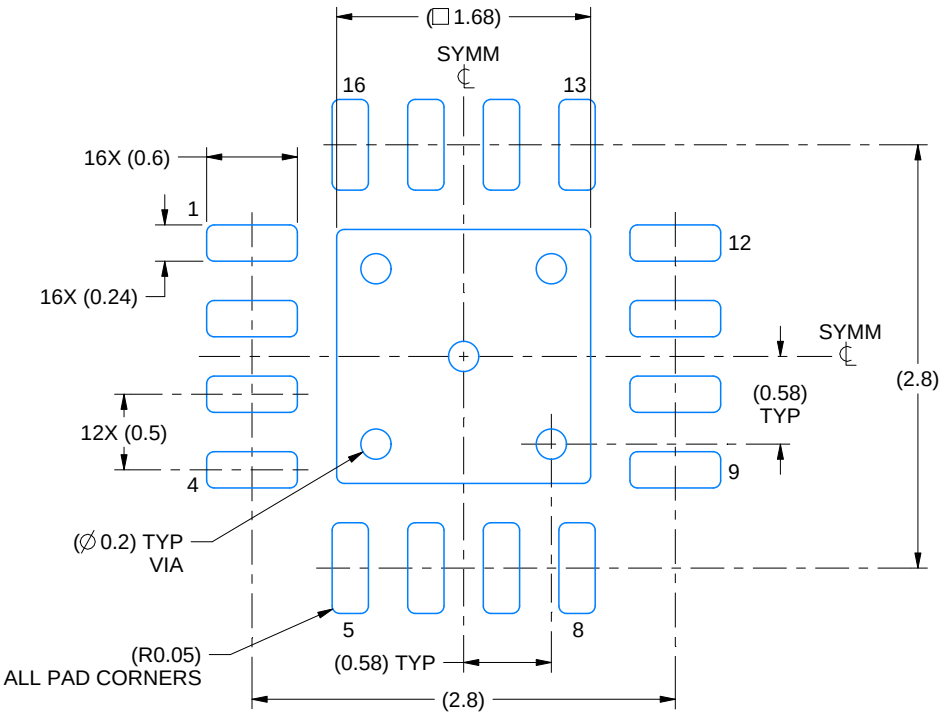
VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

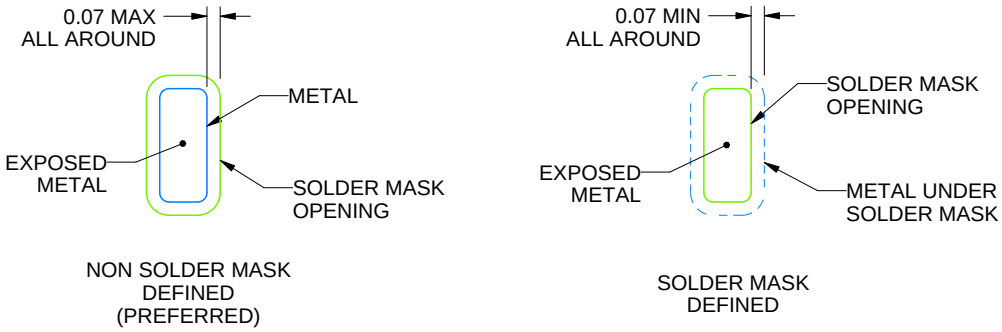


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:20X

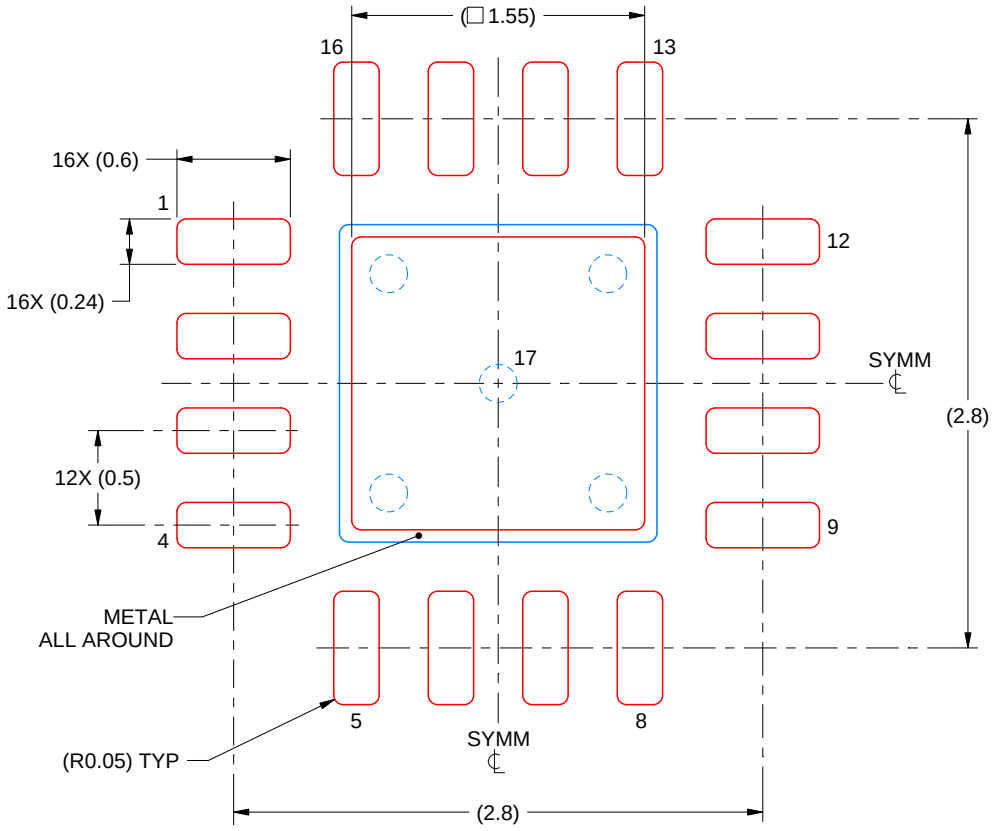


SOLDER MASK DETAILS

4222419/E 07/2025

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 17:
85% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:25X

4222419/E 07/2025

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

重要通知和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做出任何明示或暗示的担保，包括但不限于对适销性、与某特定用途的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他安全、安保法规或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的相关应用。严禁以其他方式对这些资源进行复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。对于因您对这些资源的使用而对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，您将全额赔偿，TI 对此概不负责。

TI 提供的产品受 TI 销售条款)、TI 通用质量指南 或 ti.com 上其他适用条款或 TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。 除非德州仪器 (TI) 明确将某产品指定为定制产品或客户特定产品，否则其产品均为按确定价格收入目录的标准通用器件。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

最后更新日期：2025 年 10 月